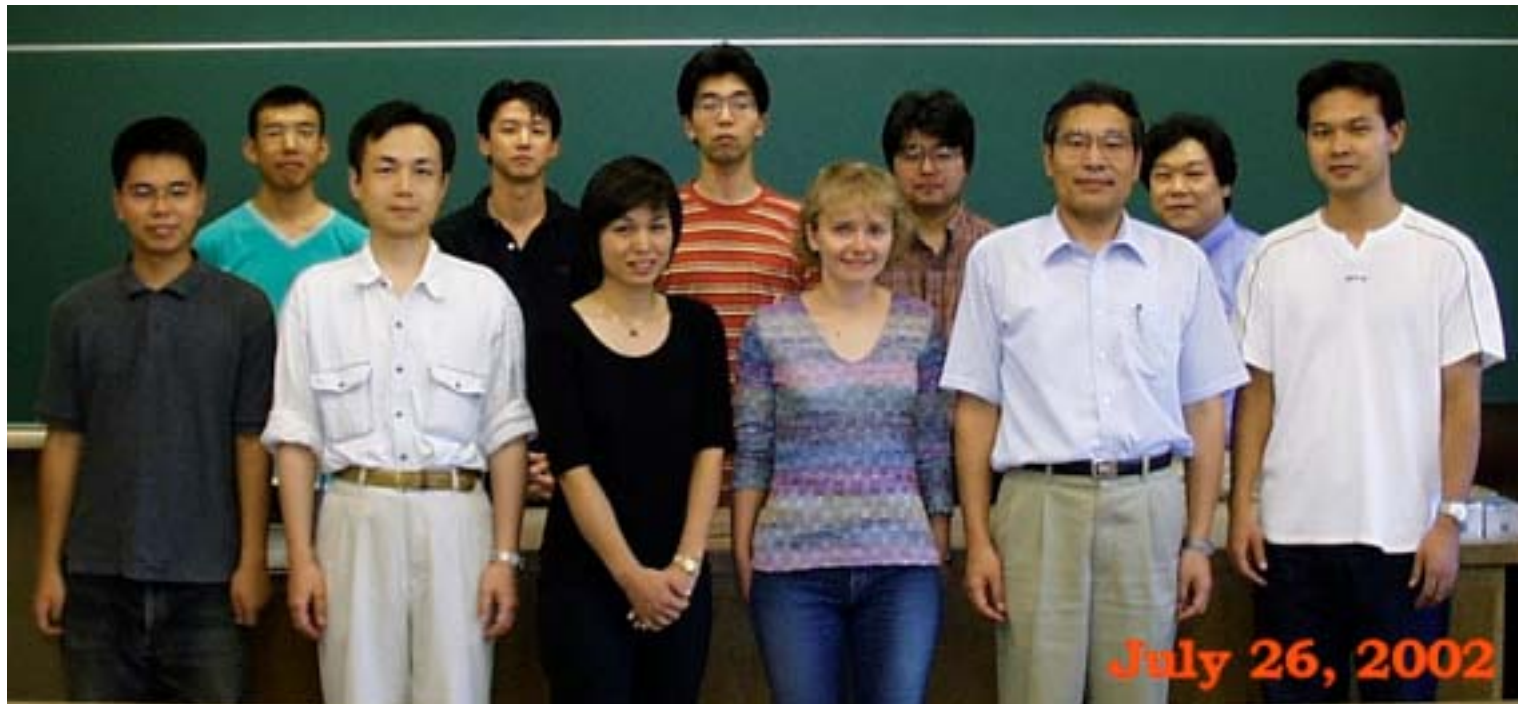


Nano-Science of Organic (Super)conductors

Gunzi Saito (Grad. School of Science, Kyoto Univ)

H.Yamochi, A.Otsuka, M.Maesato, Y.Yoshida,

K.Nishimura, O.Drozdova, D.V.Konarev, K.Balodis

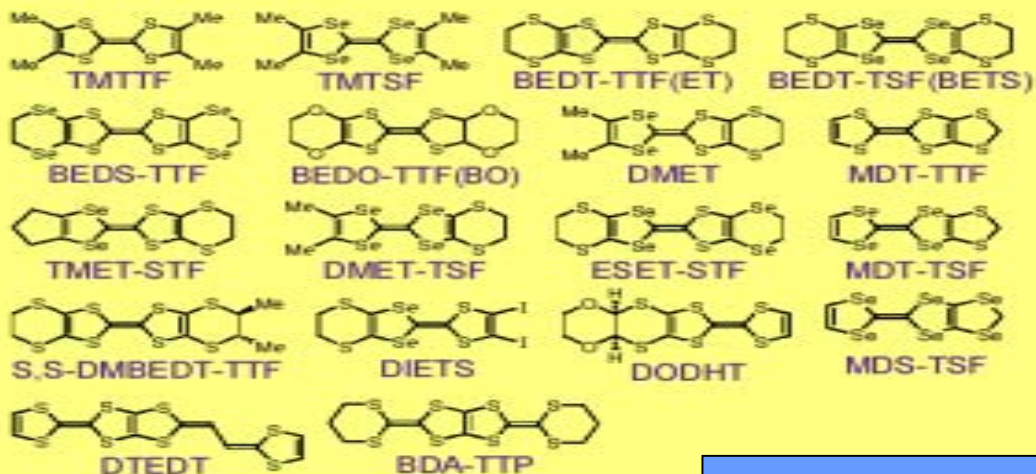


Organic Superconductors

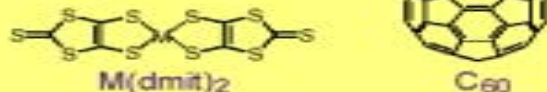
(about 120 materials since 1980)

1. Charge Transfer Complex

Donor Molecule

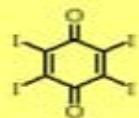


Acceptor Molecule

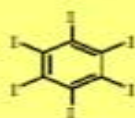


$\beta'-(\text{ET})_2\text{ICl}_2$
 $T_c(\text{on set})=14.2\text{K}$
at 82 kbar

2. Single Molecule (under pressure)



p-Iodanil



Hexaiodobenzene

Design of Organic (Super)conductors & Study of Their Physical Properties

1. Introduction

Carrier Generation & Carrier Path
On-site Coulomb Repulsion vs. Bandwidth (Mott Criterion)
Metal-Insulator or Metal-Superconductor Transition
Dimensionality Molecular Design

2. Preparation & Measurements

Crystal & Electronic (Band) Structures
Conductivity, Magnetic Susceptibility

3. 10K Class Superconductors

Electron Correlation Anisotropic Spin Lattice

4. κ -(ET)₂Cu₂(CN)₃

Ground State
Spin-Liquid (Ambient Pressure) vs Superconductor (Uniaxial Strain)

5. Conclusion

Superconductivity is Mediated by Magnetic Interactions (non BCS)

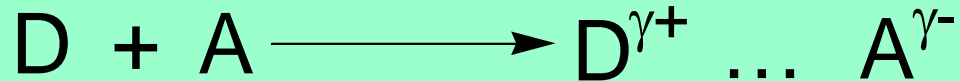
Organic Superconductor

Starting Point

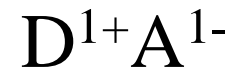
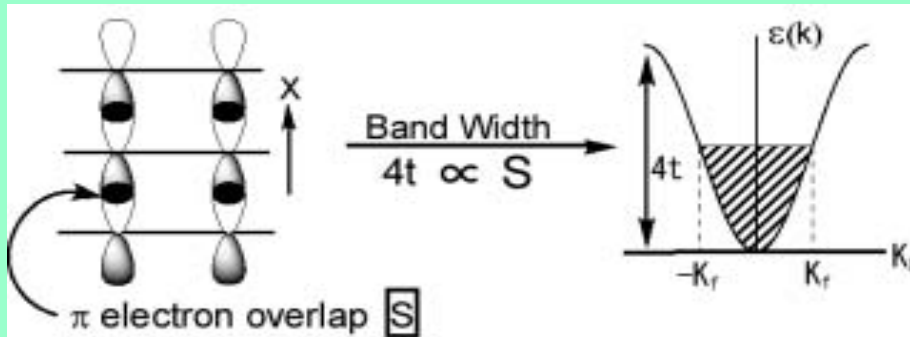
Organic Metal

- Requirement
- Generation of Carrier**
 - Generation of Conduction Path**

1: **Charge Transfer** Interaction



2: Uniform **Segregated Column**



Metal for Inorganic

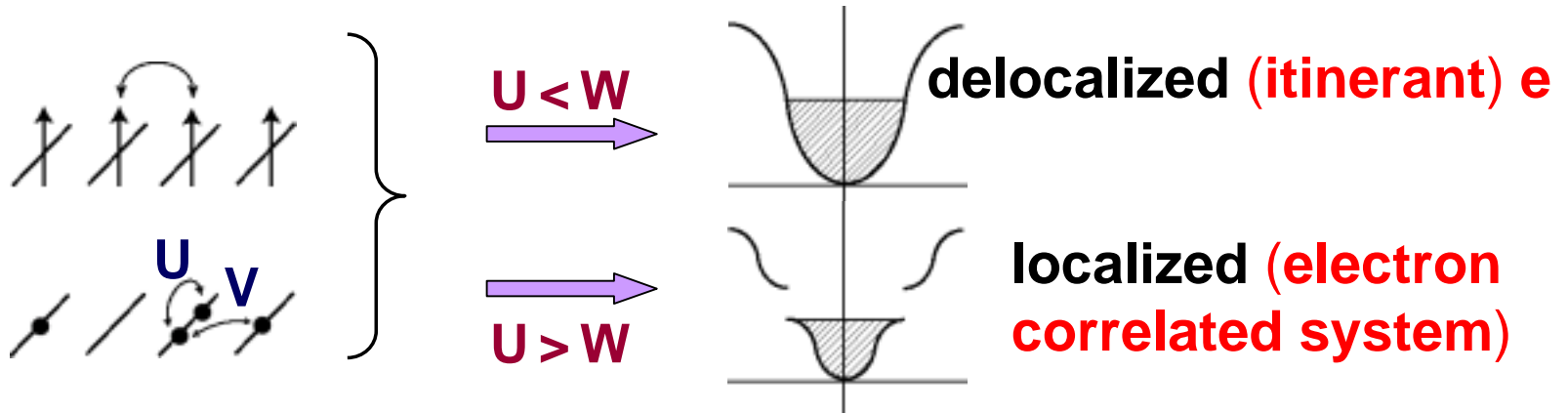
Insulator for Organic



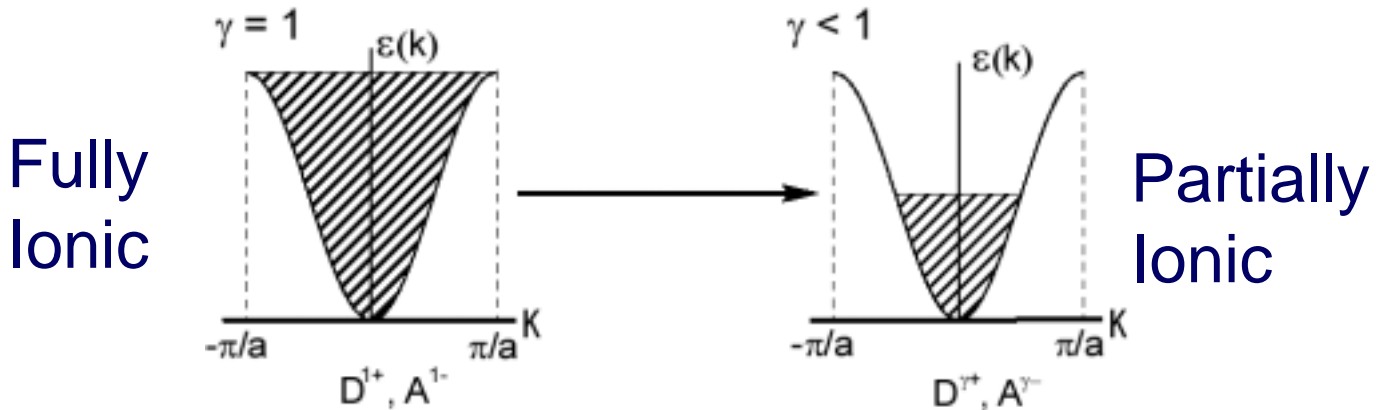
Mott Insulator

3: Mott Criterion

Organic Material \longrightarrow Bandwidth ($W = 4t$) \lesssim U



To overcome Mott criterion



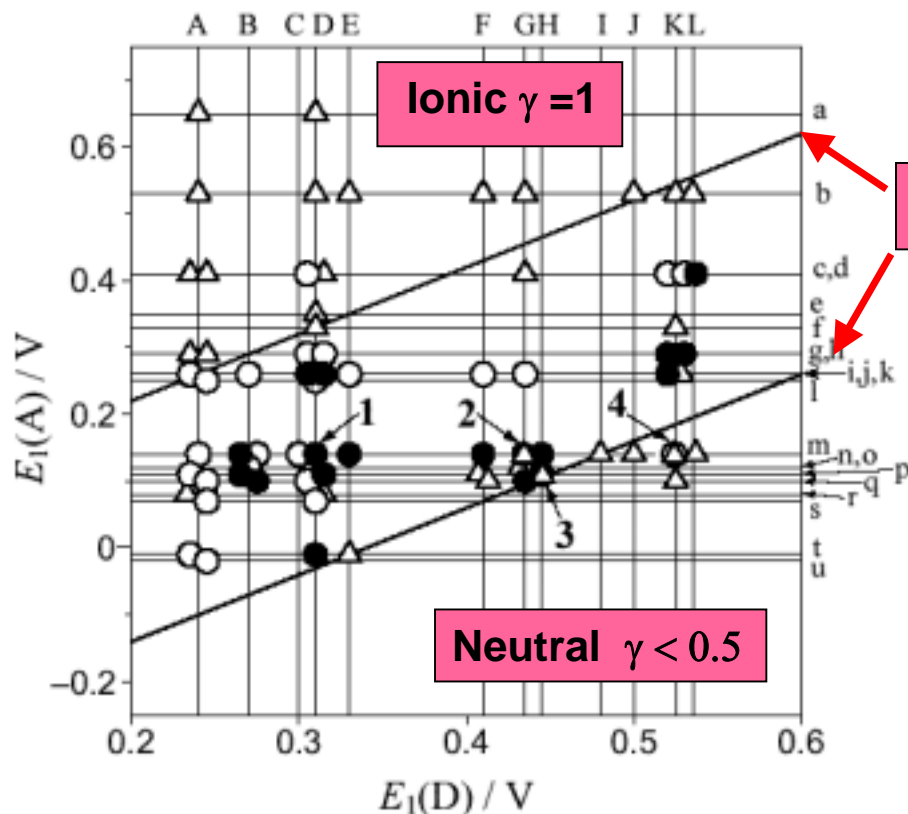
Uniform Segregated Column with Partial CT

McConnell-Hofman-Metzger Equation

Proc. Natl. Acad. Sci., USA, 53, 46(1965)

$$E_c(\gamma)/N = [(I_p - E_A)\gamma - M\gamma^2]$$

TTF•TCNQ Q-1D System



Donor

A:TTF

B:TMTTF

D:TTF

G:TMTSF

H:TSF

K:BEDT-TTF

Acceptor

b:F₄TCNQ

e:2,5-I₂

i:F

m:TCNQ

p:2,5-Et₂

: Insulator

○: Highly conducting

: Metal

1) Partial CT state

-0.02 ≤ ΔE(DA) ≤ +0.34

0.5 ≤ γ < 1

2) Complex Isomerism

TMTSF•TCNQ (2)

TSF•Et₂TCNQ (3)

ET•TCNQ (4)

↳ **2D nature of ET**

Ionic region: Mott insulator, spin-Peierls

Partial CT region: Organic Metal

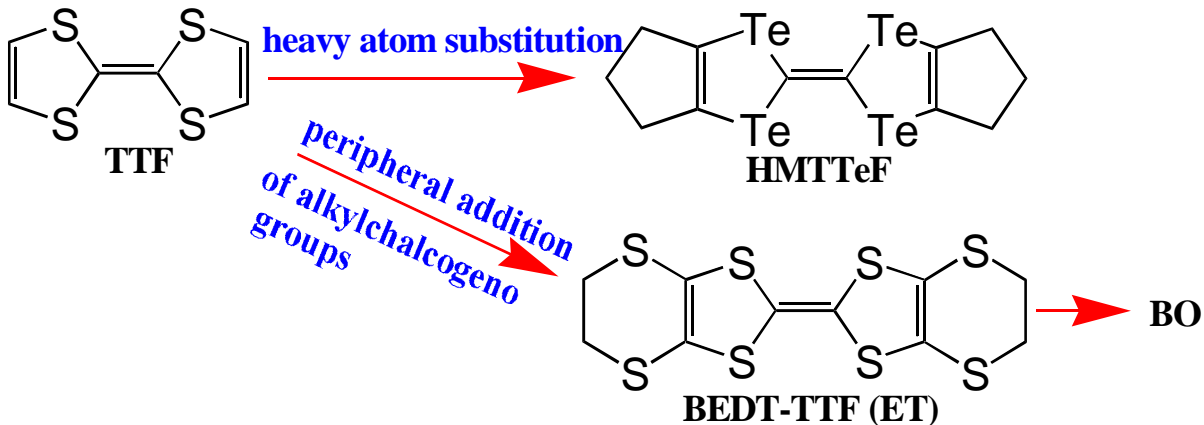
Neutral region: non-linear optics

Saito, Ferraris, BCSJ, 1980

Modification of Dimensionality & Self-Assembling Ability

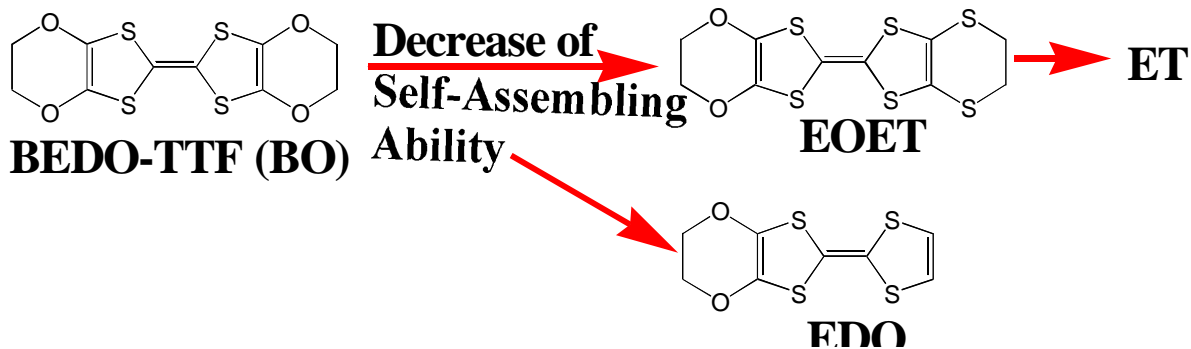
1) **Increase** of Dimensionality (self-assembling ability) : $t \uparrow$ $U \downarrow$

- γ becomes wide for 'metallic regime'
- Mott criterion becomes moderate
- One-D Fermi \rightarrow Two-D Fermi \rightarrow stable metal towards any disorder... BO system

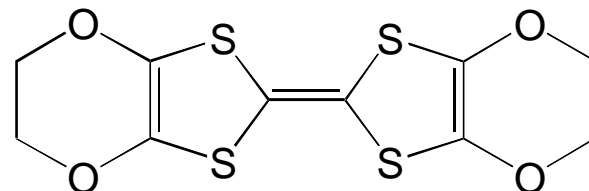
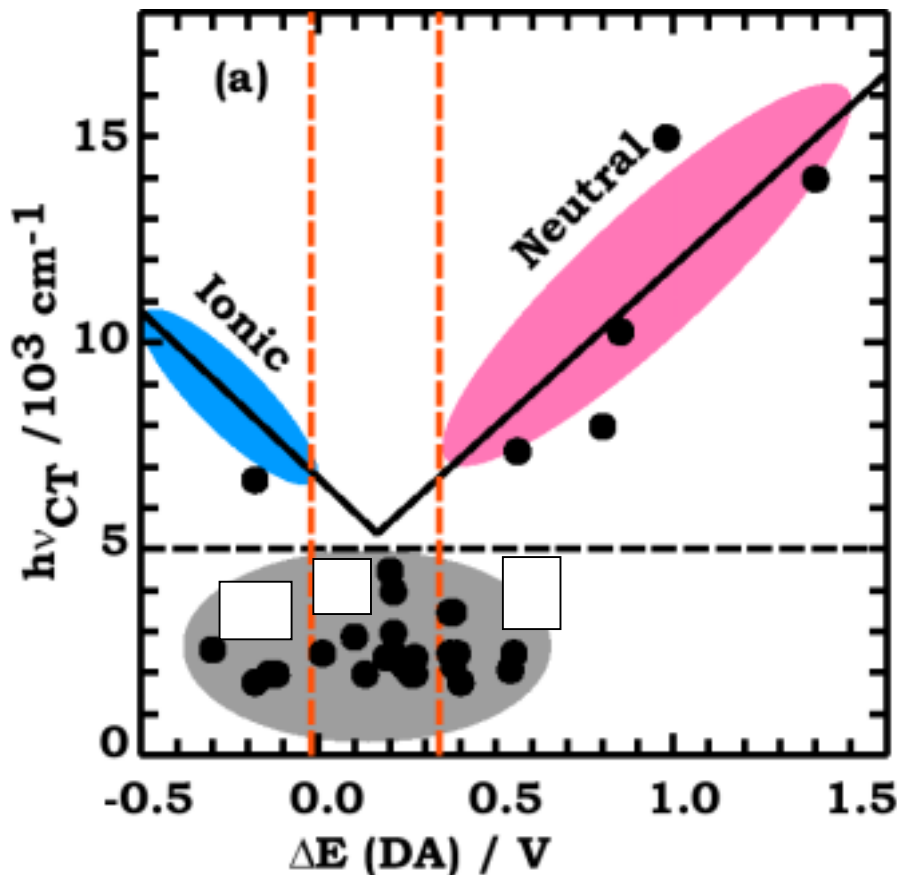


2) **Decrease** of Self-Assembling Ability: $t \downarrow$ $U \uparrow$

- **Induce Phase Instability** : New MI Phase Transition



BEDO-TTF System : Strong Self-Assembling Ability



BEDO-TTF (BO)

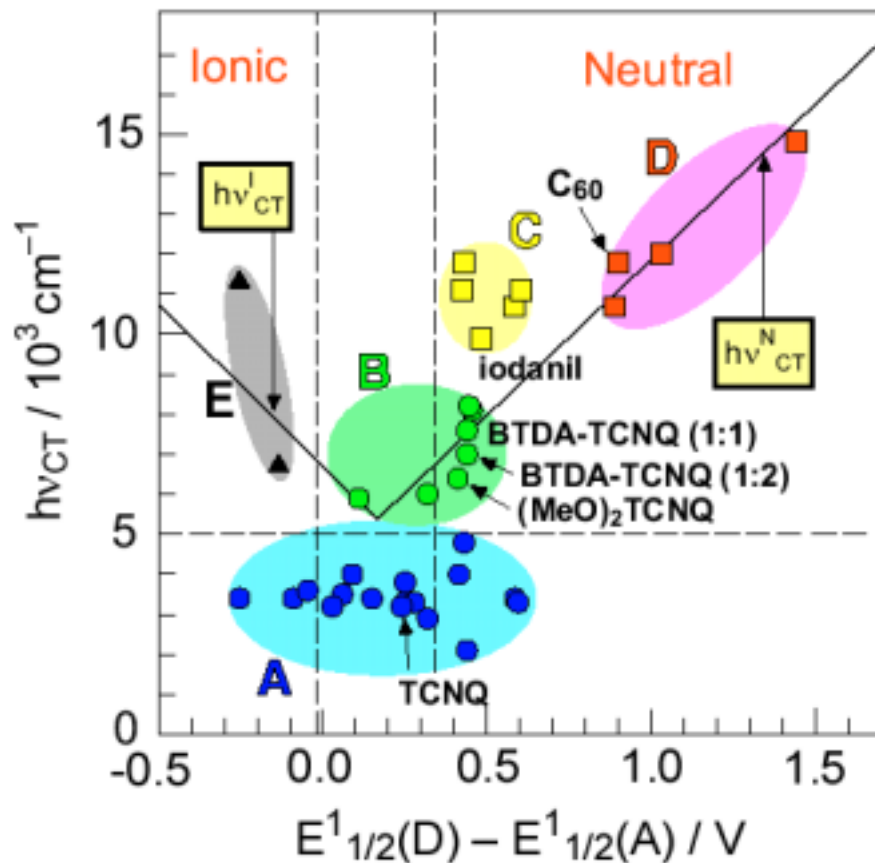
- Wide $\Delta E(\text{DA})$ for Metal
 - Stable 2D Metal
 - Strong against Disorder (Pellet, LB & RDP Films)
- JACS, 118, 8604(1996)

D:A≠1:1 (D>A)

$1 > \gamma \geq 0.5$ for TTF•TCNQ

$0.5 \geq \gamma \geq 0.3$

EOET DA Complexes



Group

A: Partial CT & Segregated

B: Partial CT & Alternating

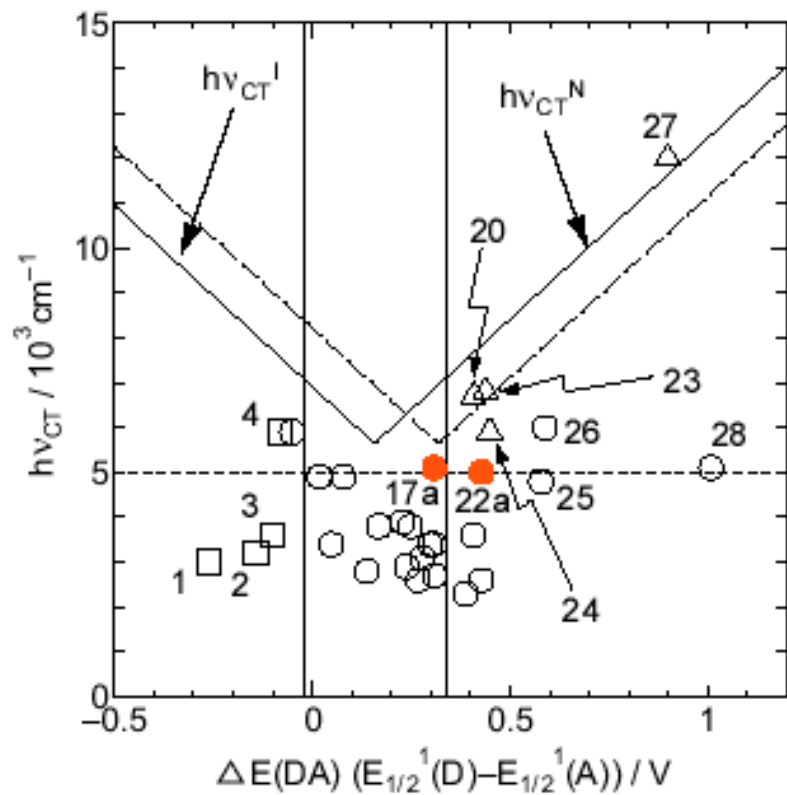
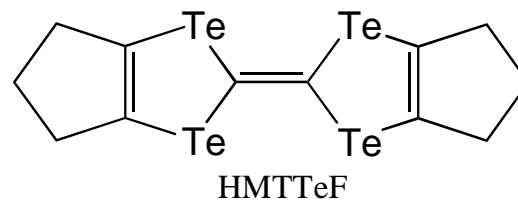
C: Clathrate

D: Neutral & Alternating

E: Ionic

G.Saito et al., J. Mater. Chem., 12, 1640(2002)

HMTTeF System



wide $\Delta E(\text{DA})$

highly conductive 10^4 Scm^{-1}

17a: $\text{HMTTeF} \cdot \text{Et}_2\text{TCNQ} \cdot (\text{THF})_{0.1-0.5}$

22a: $\text{HMTTeF} \cdot \text{BTDA-TCNQ}(\text{THF})_{0.1-0.5}$

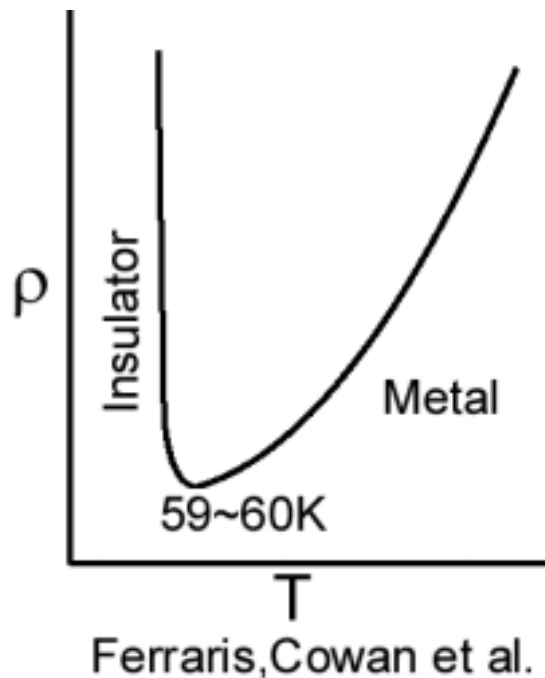
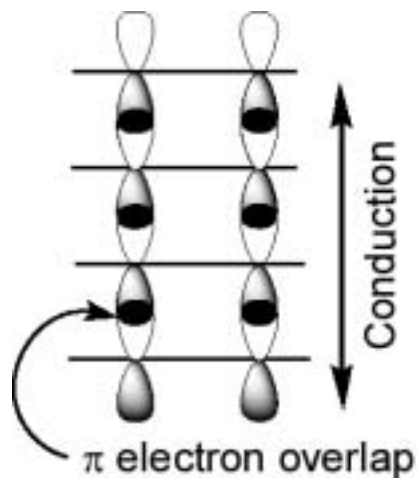
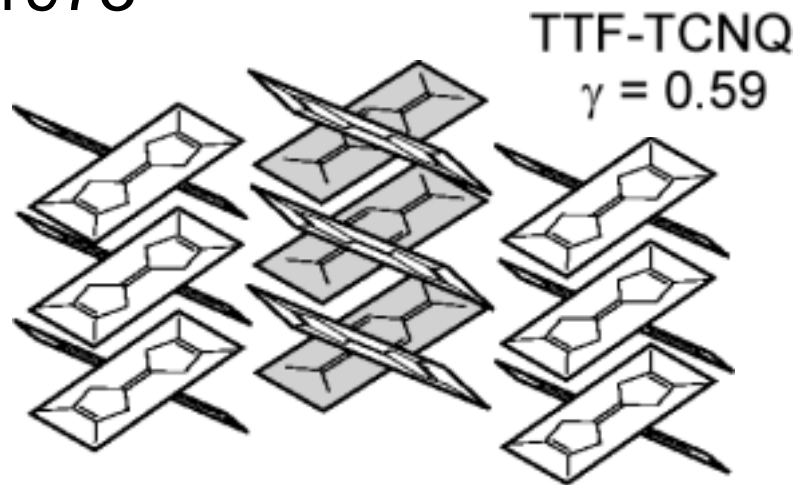
1. **Metallic (near RT)**
2. **Alternating DA Stack**

S.S.Pac, G.Saito, *J. Solid. State Chem.*, 168, 486(2002)

Organic Superconductor Starting Point

Suppress the M-I Transition of Low-dimensional Metal

1973~



One-dimensional Metal

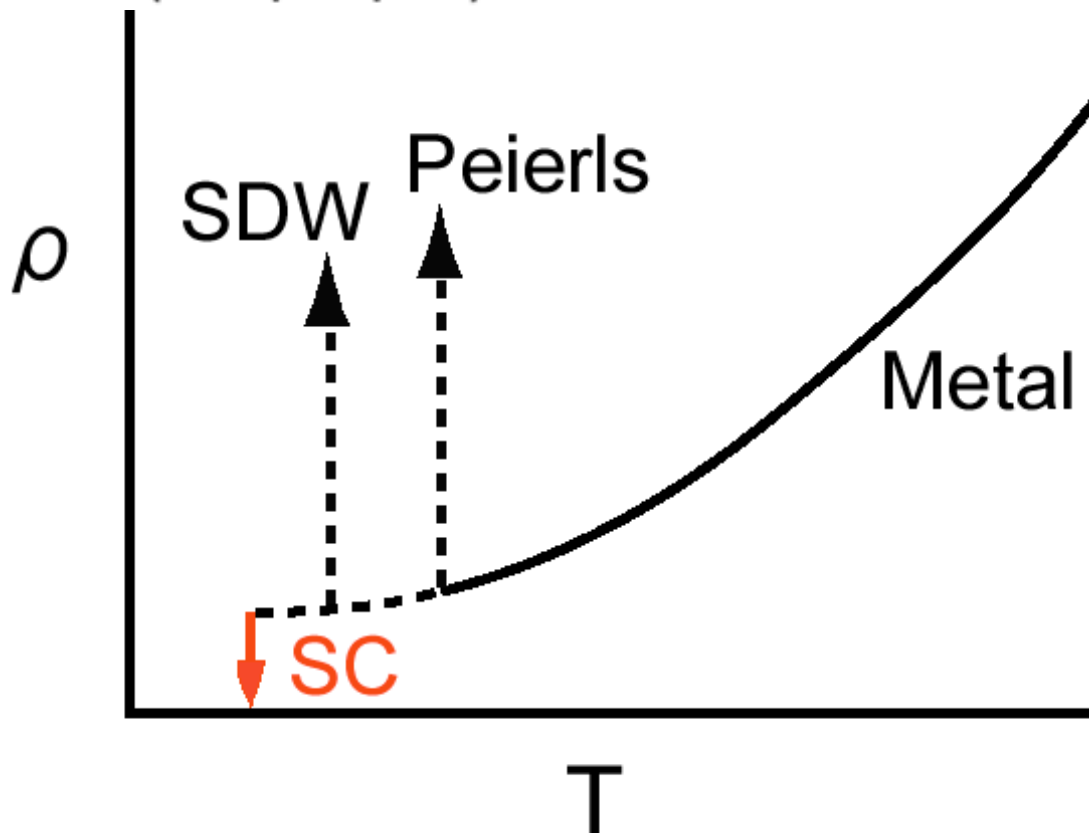
Three Low-temperature Phases of Low-dimensional Metal

1. Peierls (electron-phonon)

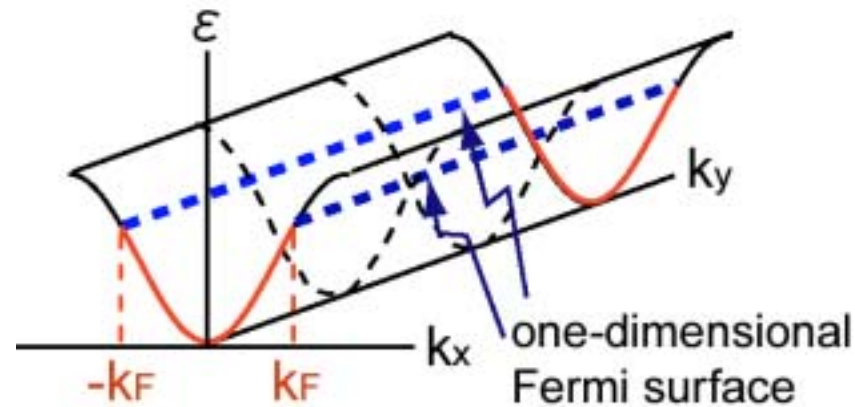
2. SDW (spin-spin)

3. **SC** (Cooper pair)

Organic Metal \rightarrow Peierls Insulator



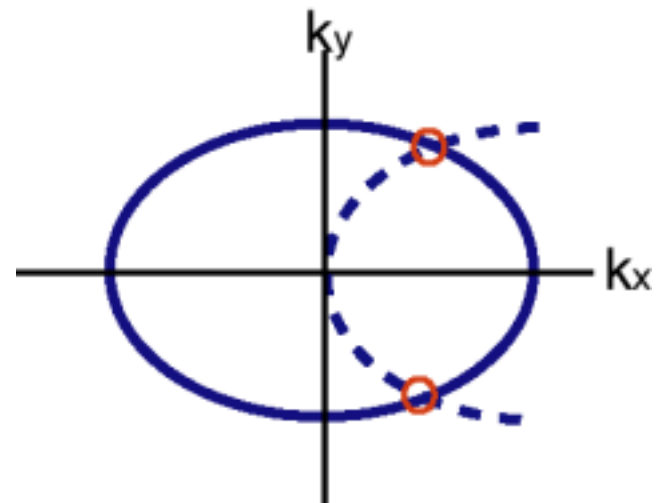
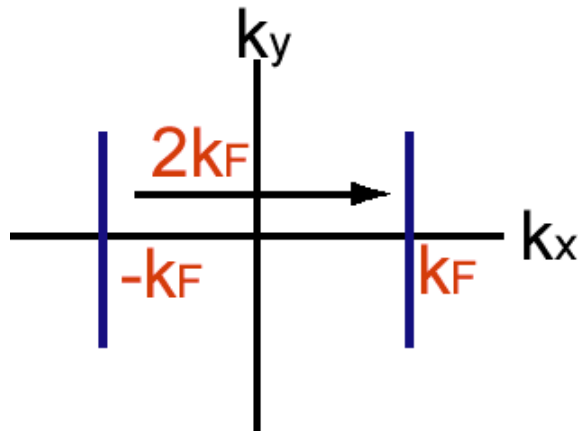
How to Suppress the Peierls Transition (in k space)



avoid $2k_F$ nesting
increase dimensionality



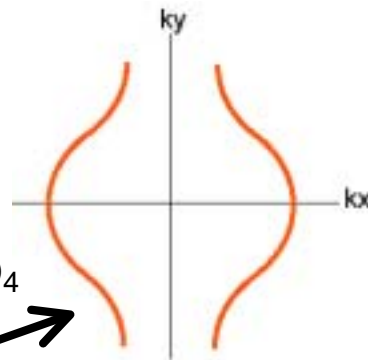
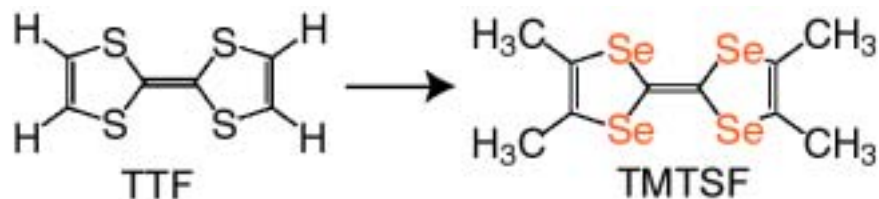
two-dimensional
Fermi surface



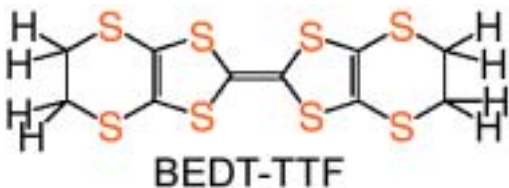
How to Suppress the Peierls Transition (in real space)

1. S → Se 1980 Bechgaard, Jerome

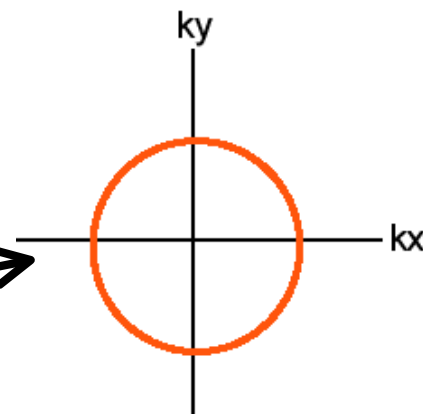
One-dimensional $(\text{TMTSF}^{0.5+})_2\text{X}$, $\text{X}=\text{ClO}_4$



2. S → S + S



1982 Two-dimensional Metal
no MI Transition
Saito, Enoki, Toriumi, Inokuchi



3. C₆₀ $(\text{M}^+)_3\text{C}_{60}^{3-}$, $\text{M}=\text{K}, \dots$

1991 Three-dimensional Metal
Hebard, Haddon et al.

Design of Functional Molecular Materials

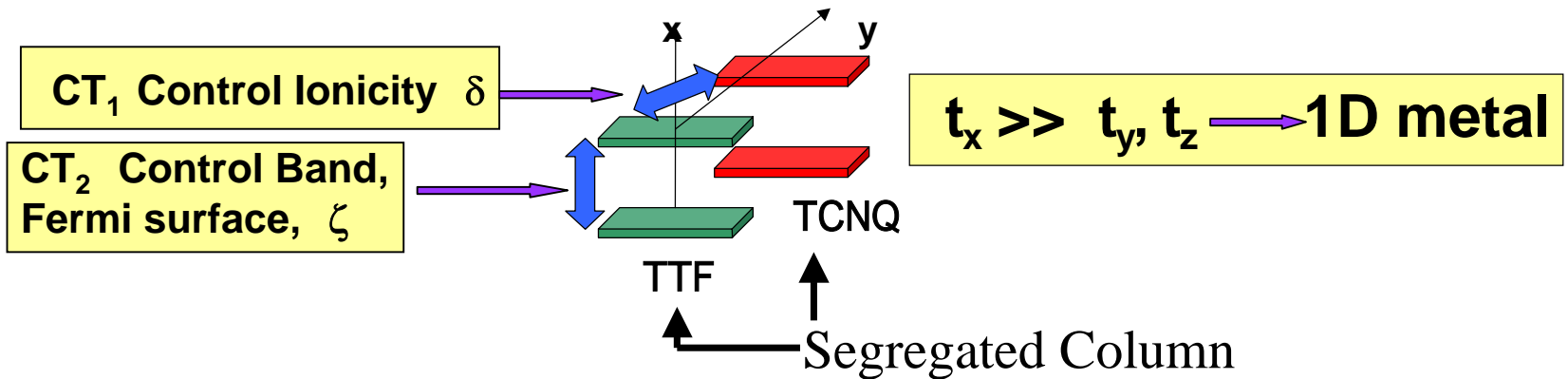
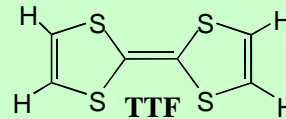
Structure (Molecule, Crystal, Electronic, Band)
vs **Function**

Weak Intermolecular Interaction

CT (π - π , n- π), **Hydrogen Bond**(CH \cdots O), **vdW**(S \cdots S, Se \cdots Se, Te \cdots Te), **Coulomb**(Madelung, on-site off-site **electron correlation**)

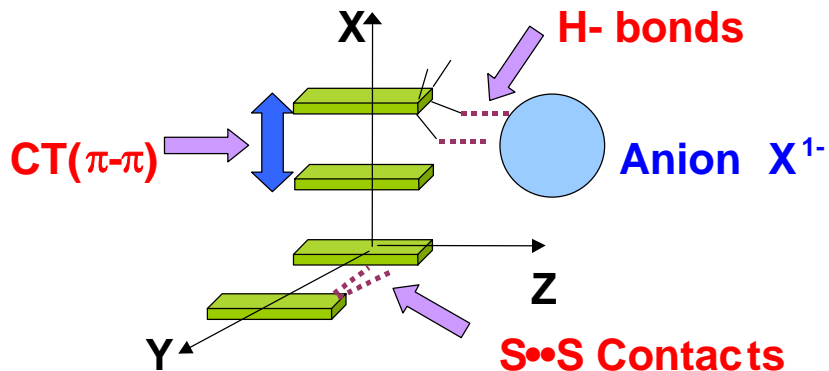
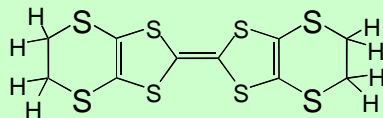
CT:
e Donor + e Acceptor (or Anion)

1) TTF $^{\delta+}$ TCNQ $^{\delta-}$ ($\delta=0.59$)



2) (BEDT-TTF^{δ+})₂X

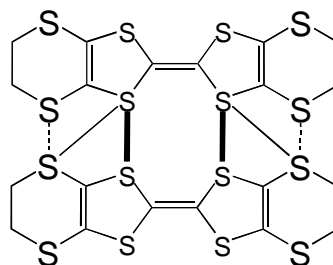
δ=0.5 1 hole / dimer



S · · S Contacts

$$(\text{S}_{\text{in}} \cdot \cdot \text{S}_{\text{in}}) : (\text{S}_{\text{in}} \cdot \cdot \text{S}_{\text{out}}) : (\text{S}_{\text{out}} \cdot \cdot \text{S}_{\text{out}}) = 10 : 3.6 : 1$$

For ET salts: no S_{in} · · S_{in} contact



$$t_x \sim t_y \gg t_z$$

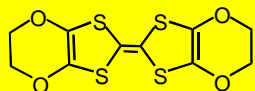
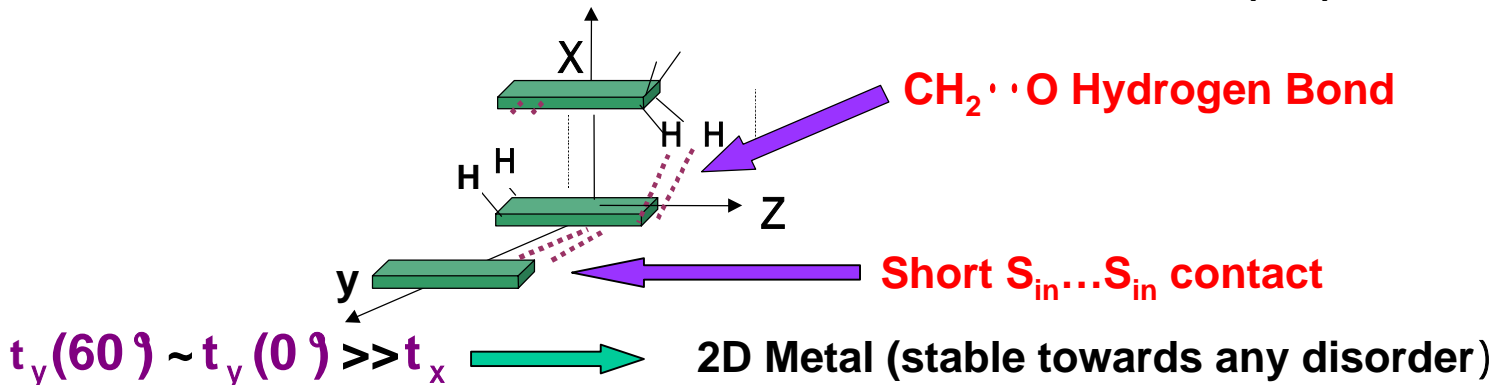
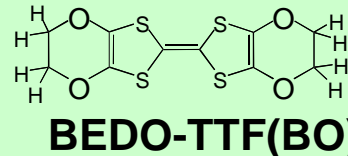
2 Dimensional

face-to-face (π-π) & side-by-side (S · · S) compete
Hydrogen bond (CH-X) modifies electronic structure

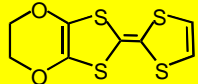
varied ethylene conformation

Polymorphism (α, α', β, β', β'', θ, κ · · ·)

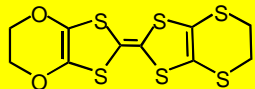
4) (BEDO-TTF)₂X Self-assembling Ability



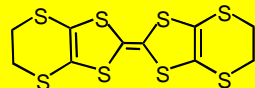
Metallic LB films, Metallic transparent films (self-assembling)



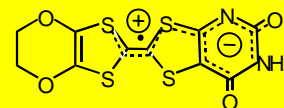
New Metal-Insulator Transition (molecular deformation)



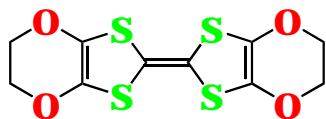
Two-leg Spin-ladder (molecular symmetry C_{2v})



Spin-liquid vs Superconductor (e-correlation U/W, t'/t)

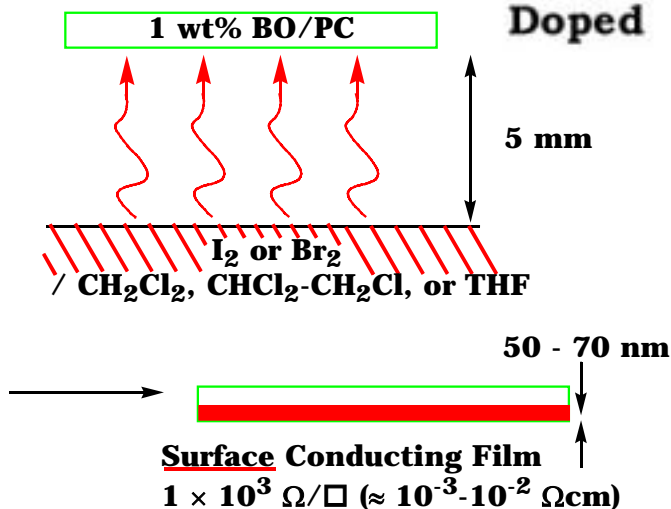


Molecular Electronics (mean free path vs e-correlation)



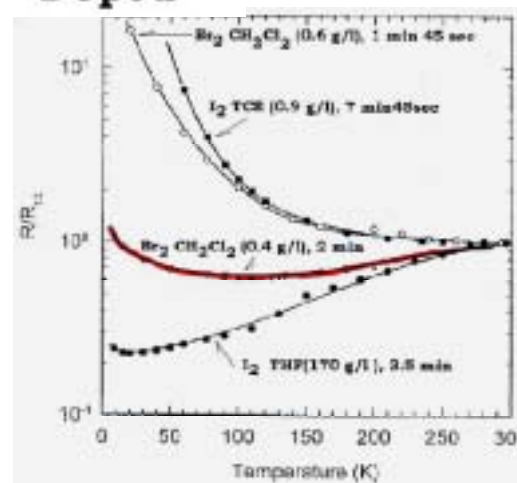
BEDO-TTF (BO)

·Film Preparation



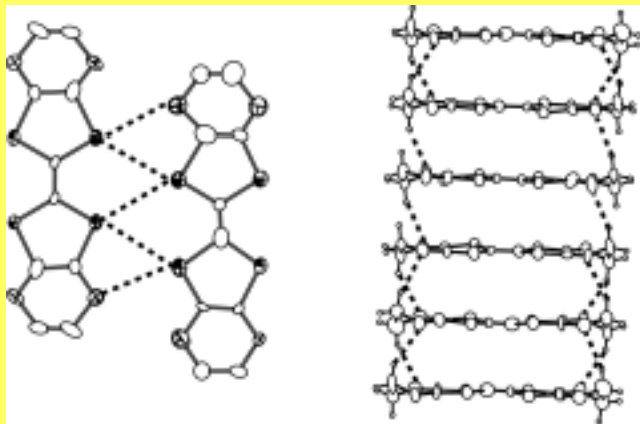
Iodine Doped

Bromine Doped

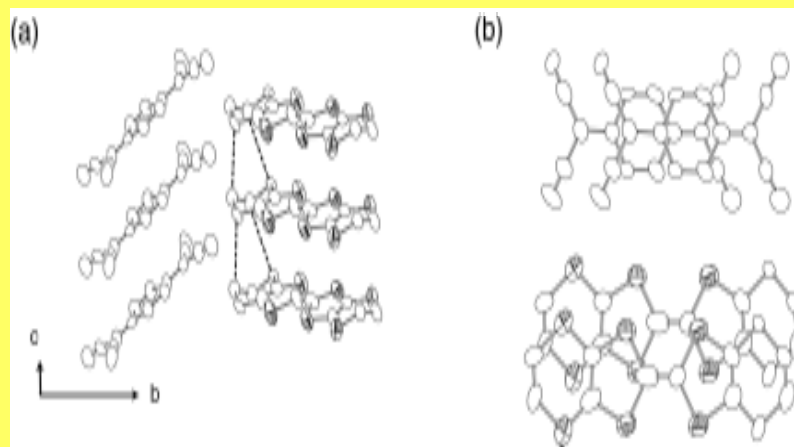


JMC 10, 893-910(2000) M(dto)₂, 10, 911-919(2000) TNBP, 11, 364-373(2001) DHCP, JACS 122, 4436-4442(2000) degree of CT, Synth. Metals, 120, 721, 739, 863 (2001) plasmons, design, MCLC, 376, 113-120(2002) MM'(ox)₃, JSSC, 168, 450-456(2002) M(isoq)₂(NCS)₄

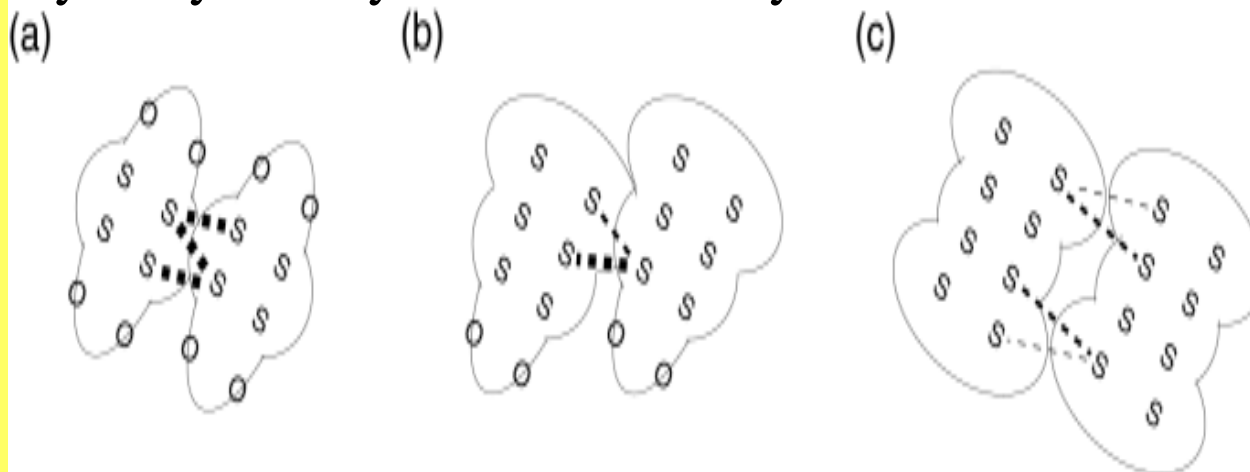
Stacking of BO molecules



Stacking of EOET molecules



Geometry & Symmetry effect on side-by-side atomic contacts



BO

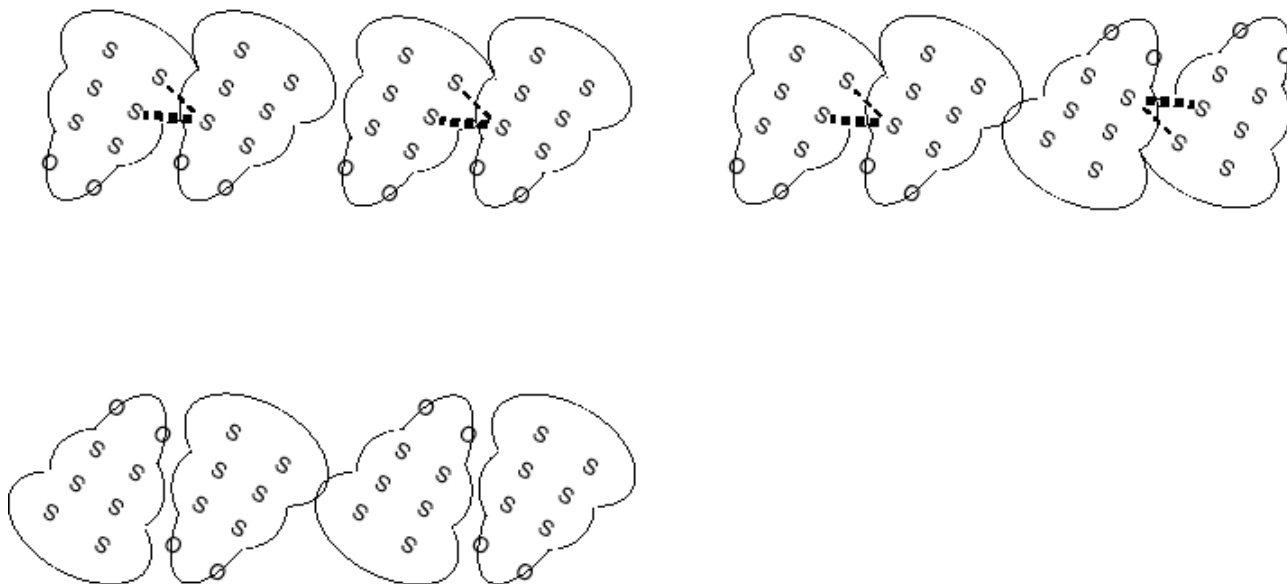
EOET(head-to-head)

ET

Design of Two-Leg Spin-Ladder based on EOET

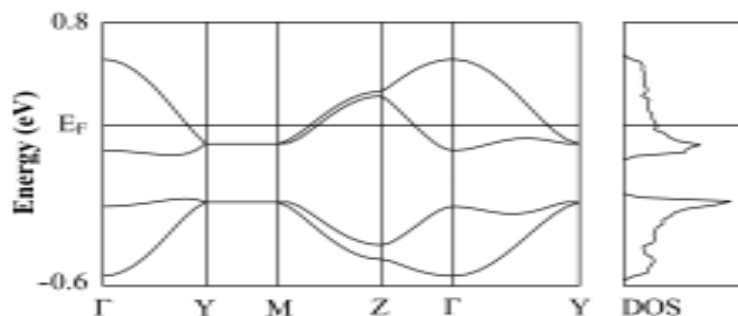
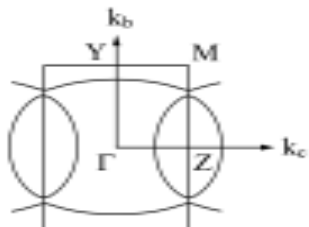
G. Saito et. al.

Figure 04

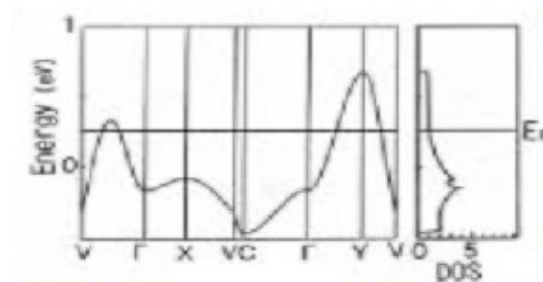
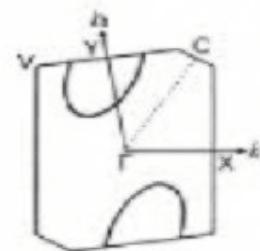


Energy Dispersion, Fermi Surface, DOS

κ -(ET)₂Cu(NCS)₂

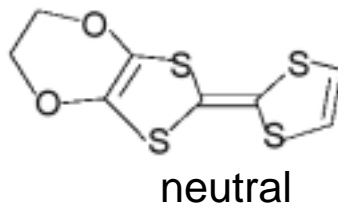
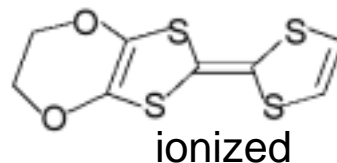
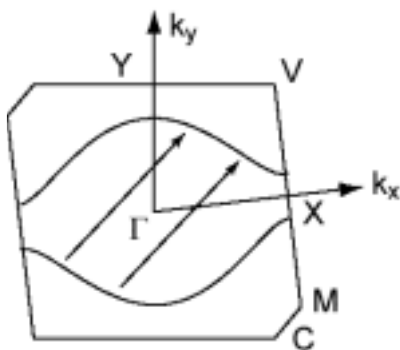


(BO)_{2.4}I₃



2D → 1D

(EDO)₂PF₆



New Metal-Insulator
Transition triggered by
molecular deformation

Ota, Yamochi, Saito
J. Mater. Chem., 12,
2600(2002)

Summary(1)

1. Uniform Segregated Column with Partial CT
controllable by Self-assembling Ability & (I_P - E_A)

2. Dimensionality

controllable by physical (pressure) & chemical
"heavy atom substitution" "peripheral addition
of alkylchalcogeno groups" methods
(size, symmetry, degeneracy)

1D TTF

1~2D ET

EOET

2D BO

Stability

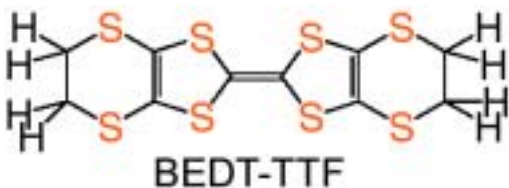
&

Self-Assembling Ability



Preparation & Characterizations of 10 K Class Superconductors

	Tc/K	
	H	D
κ -(ET) ₂ Cu(NCS) ₂	10.4	11.2
Cu[N(CN) ₂]Br	11.8	11.2
Cu[N(CN) ₂]Cl	12.8	13.1 (at 0.3kbar)
Cu(CN)[N(CN) ₂]	11.2	12.3

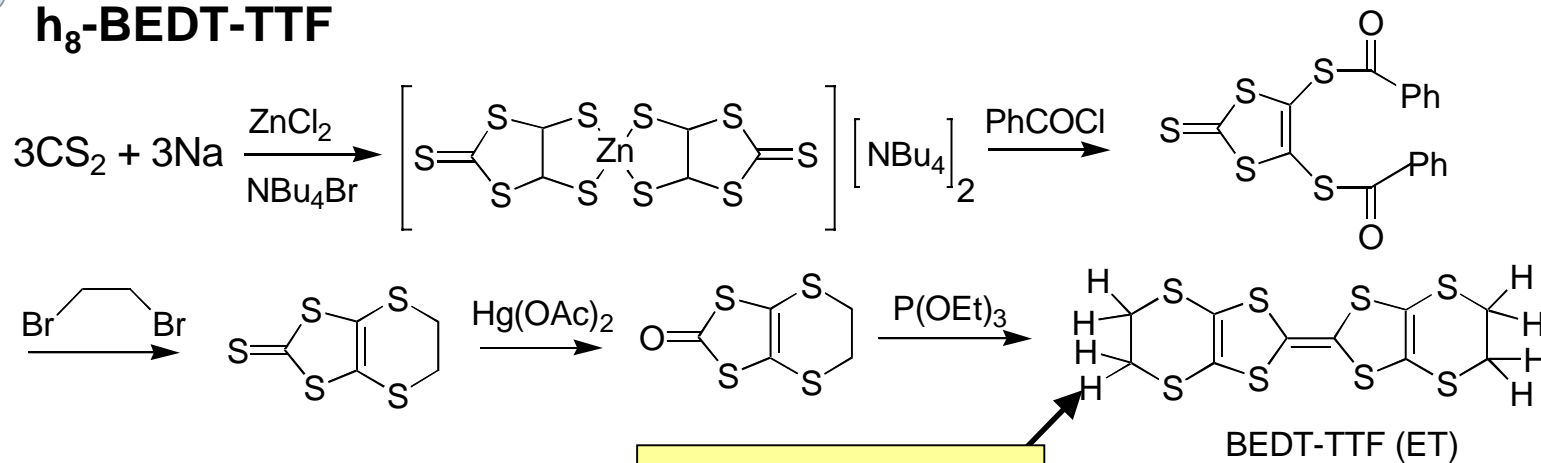


H-Salt

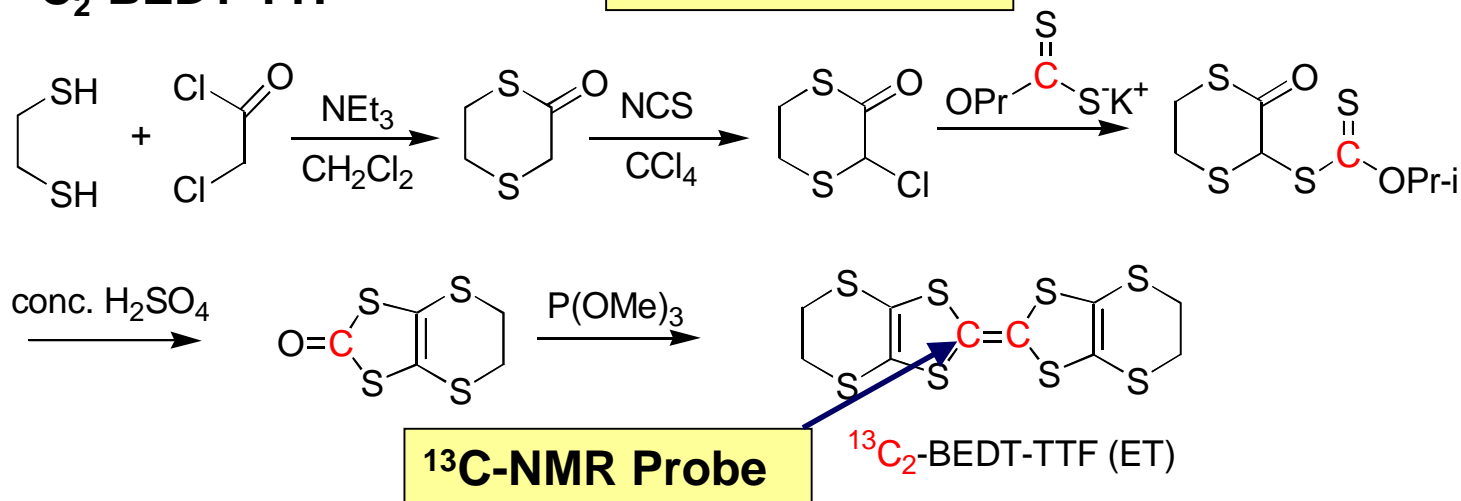
H → D-Salt

Synthesis of BEDT-TTF (ET)

h_8 -BEDT-TTF



$^{13}\text{C}_2$ -BEDT-TTF



Long Symmetric Linear Anion ?

NCS - Cu - SCN
~ 15 Å

vs

I - I - I⁻
10.1 Å $\beta\text{-(ET)}_2\text{I}_3$ $T_c = 8\text{K}$

Electrocrystallization

1. Supporting Electrolyte

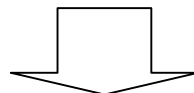
$\text{CuSCN} + \text{KSCN} + 18\text{-crown-6 ether}$
70 mg 130 mg 200 mg

K^+ , SCN^- , CuSCN

2. Donor $\text{BEDT-TTF} \longrightarrow \text{BEDT-TTF}^{\oplus}$

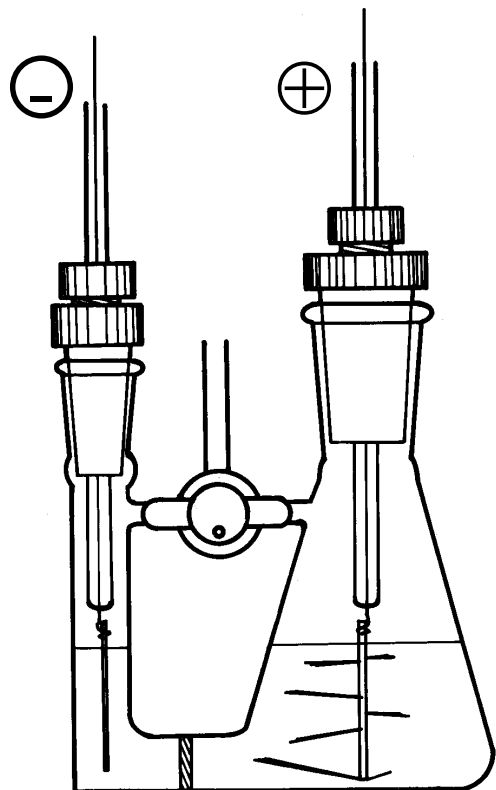
3. Solv 1,1,2-trichloroethane or benzonitrile

4. Current 0.5 ~ 4 μA , ~2 weeks

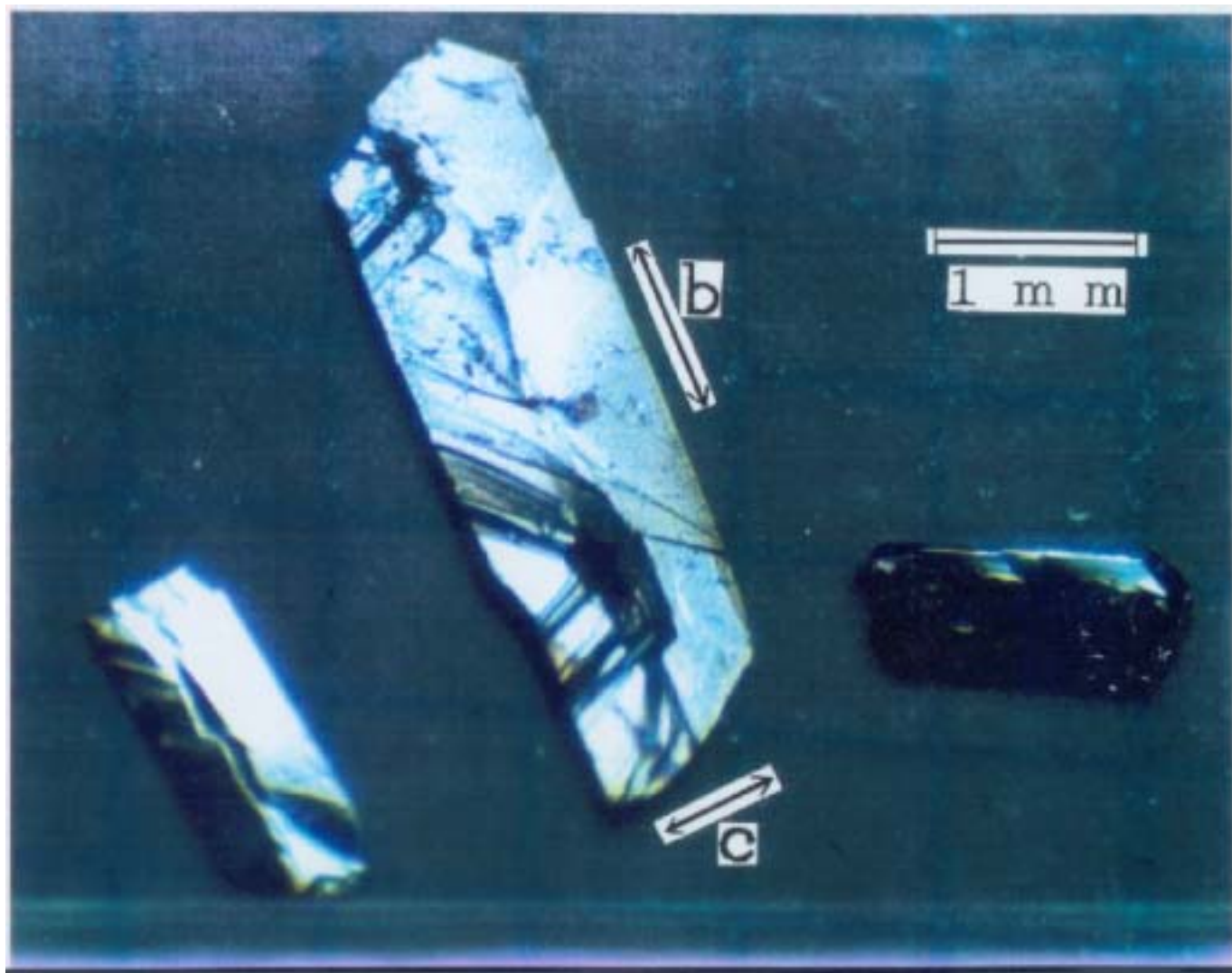


$(\text{BEDT-TTF})_2\text{Cu}(\text{NCS})_2$

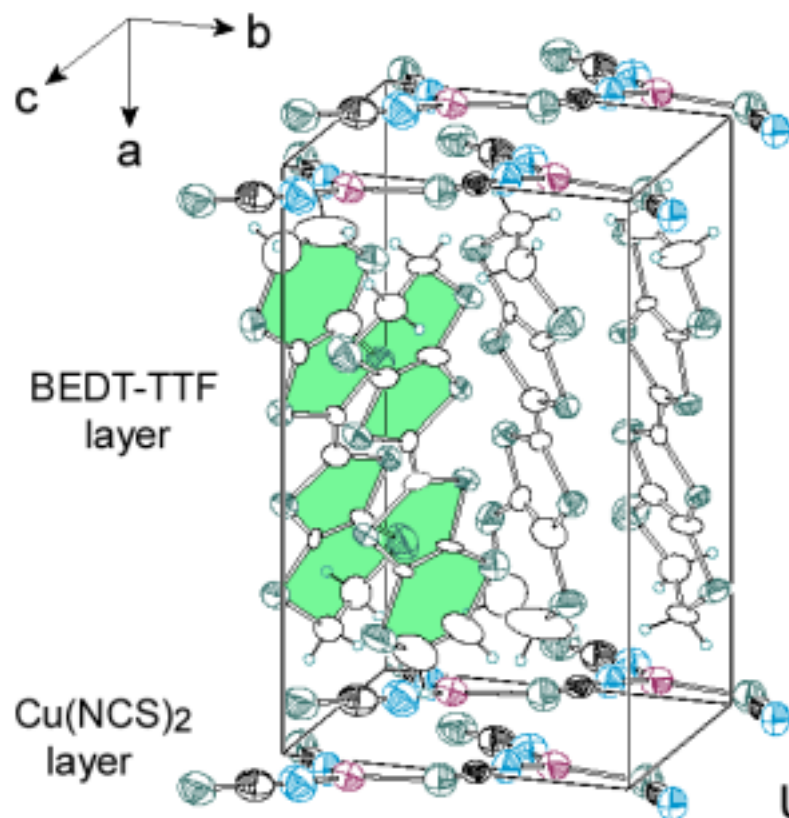
1988 Urayama, Saito *et al.*



κ -(BEDT-TTF)₂Cu(NCS)₂ bc-plane: 2D conducting

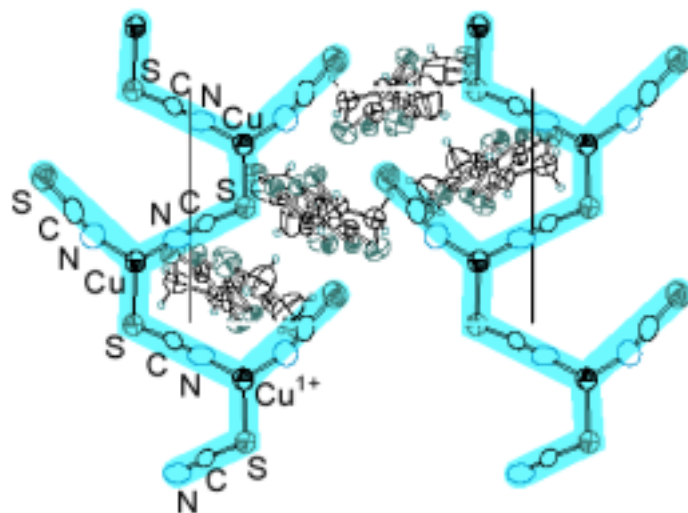


κ -(BEDT-TTF)₂Cu(NCS)₂



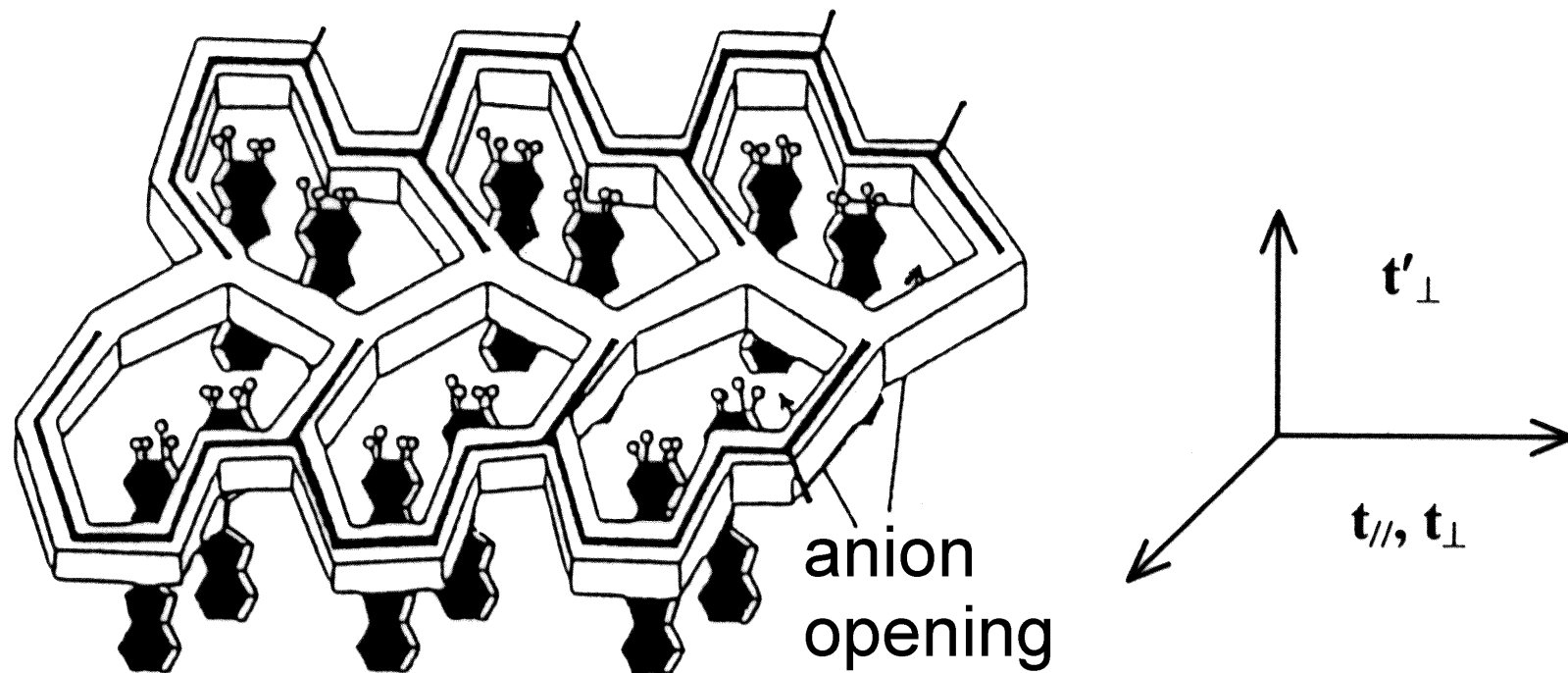
[dextro rotatory form]

monoclinic $P2_1$



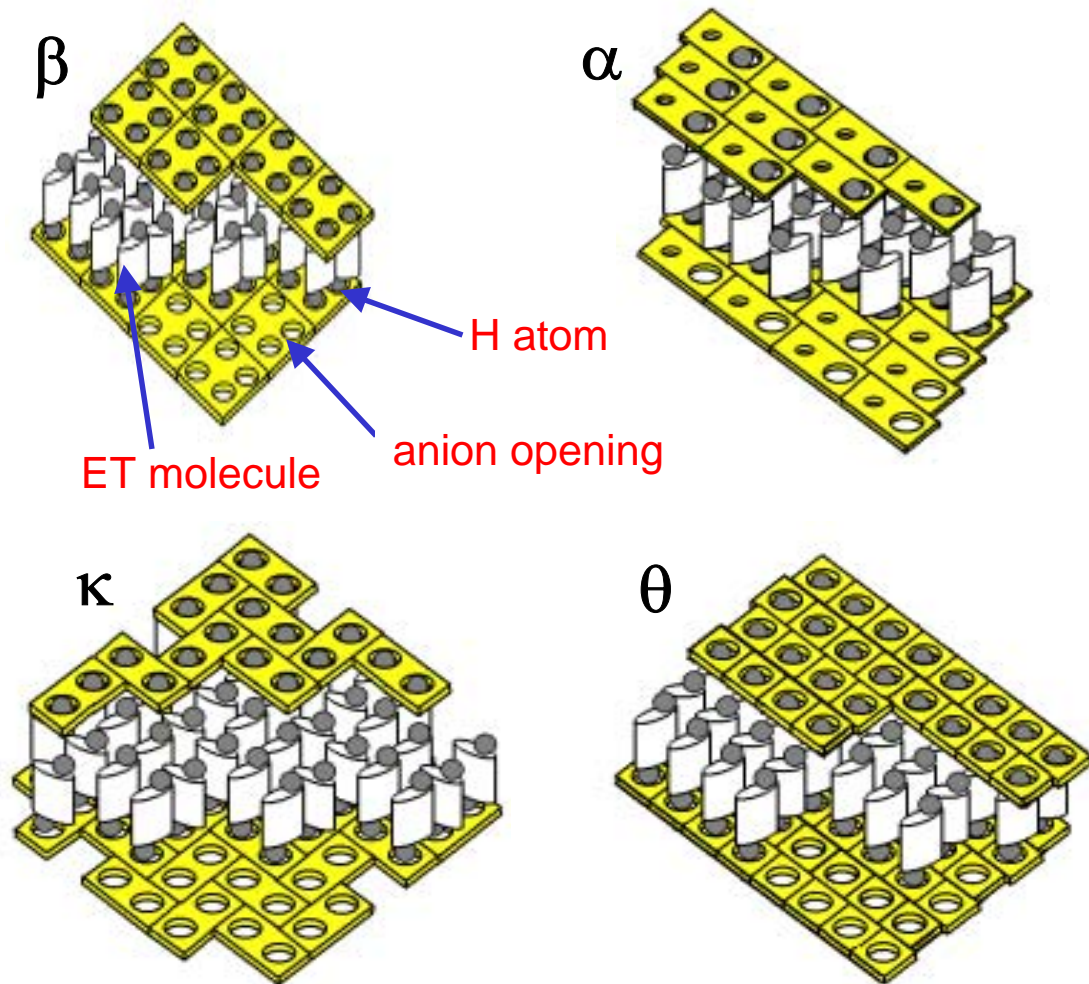
Urayama, Saito *et al.*,
Chem. Lett., 1988, 55

κ -(BEDT-TTF)₂X, X:polymerized anion



1. Pattern \longrightarrow donor packing pattern
2. Basal Plane Size \longrightarrow $t_{//}$, t_{\perp} , DOS
3. Thickness \longrightarrow t'_{\perp}

Patterns of Anion Opening & Donor Packing



H.Yamochi et al., JACS, 115, 11319(1993)

Design of High T_c ET Superconductors

1. Big anion \rightarrow Packing density of ET $\downarrow \rightarrow t_{//} \downarrow \rightarrow$ DOS $\uparrow \rightarrow T_c \uparrow$

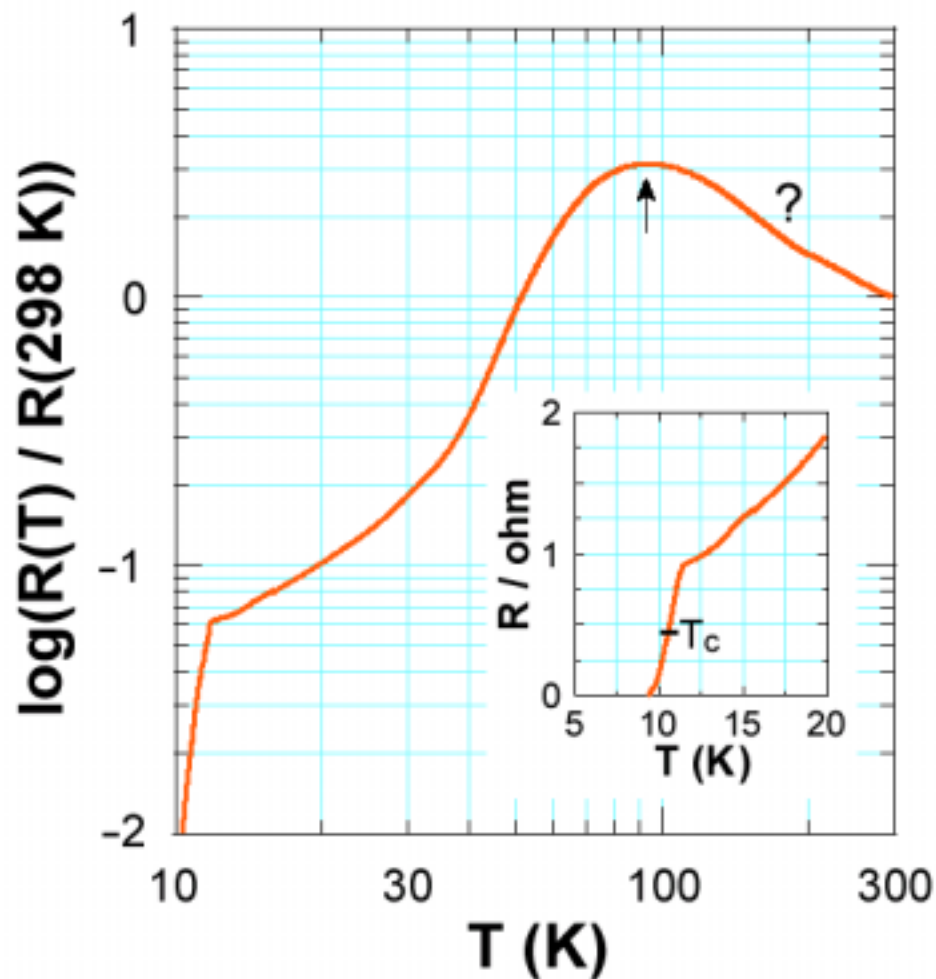
2. Thin anion \rightarrow Inter-donor-layer $t'_{\perp} \uparrow \rightarrow$ 3D nature $\uparrow \rightarrow T_c \uparrow$

3. 2D polymerized anion + donor-anion interaction $\uparrow \rightarrow$
3D structural nature $\uparrow \rightarrow$ thermal contraction $\downarrow \rightarrow$
keep DOS large $\rightarrow T_c \uparrow$



Use **big** and **thin** anion which forms **thin 2D anion layer**
and provides both
loose donor packing and **strong anion•••donor atomic contacts**

κ -(BEDT-TTF)₂Cu(NCS)₂



4 probe Au wire Au paste

$$\sigma_{RT}(\parallel b) = 10 \sim 40 \text{ S cm}^{-1}$$

$$\sigma_{a^*} : \sigma_b : \sigma_c = 1/600 : 1 : 1.2$$

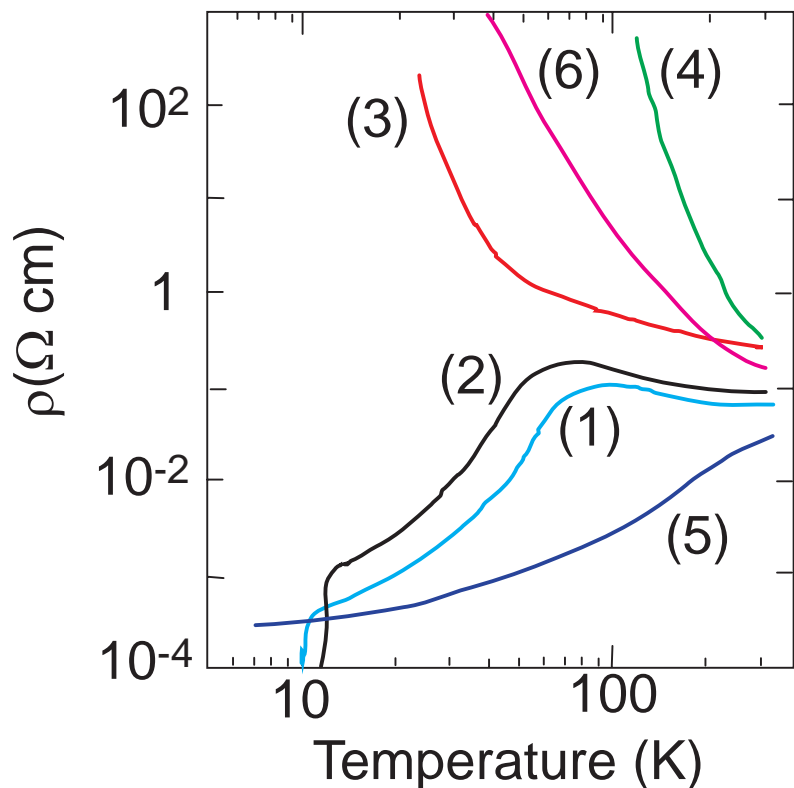
T_c on set : 11.0 K

off set : 9.8 K

mid-point : 10.4 K

Pressure $\uparrow \rightarrow T_c \downarrow$
(-3.0 K/kbar)

Resistivity for ET Salts



10K Class Superconductor

(1) κ -(ET)₂Cu(NCS)₂

(2) κ -(ET)₂Cu[N(CN)₂]Br

(3) κ -(ET)₂Cu[N(CN)₂]Cl

Mott Insulator at Ambient

Superconductor at 0.3kbar

Electron Correlated Insulator

(4) θ -(ET)₂Cu₂(CN)[N(CN)₂]₂

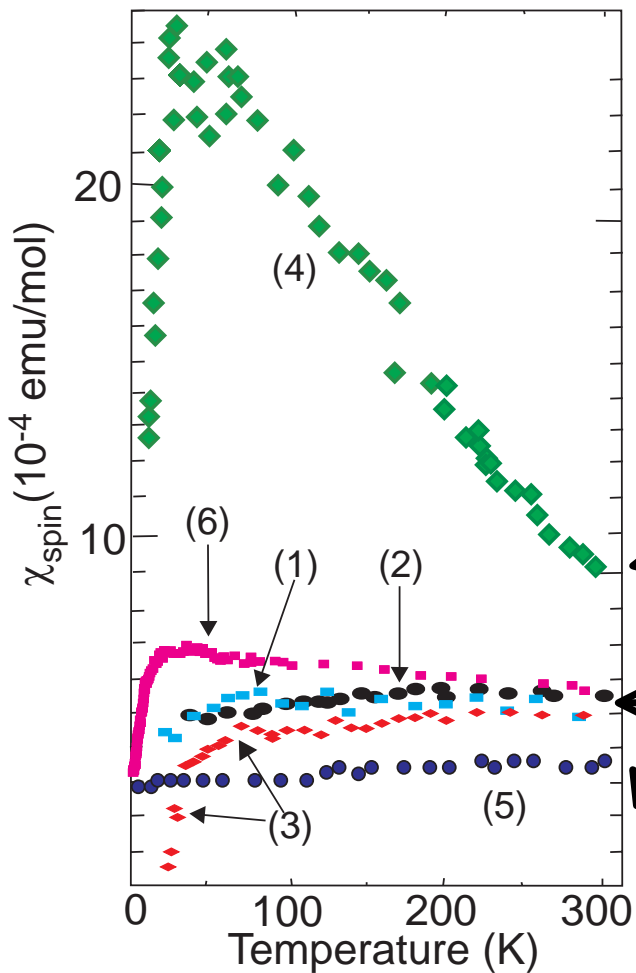
2D Metal with low T_c

(5) β -(ET)₂AuI₂

What about

(6) κ -(ET)₂Cu₂(CN)₃ → Mott Insulator

EPR Magnetic Susceptibility χ_{spin}



For a metal $\chi_{\text{spin}} = \chi^0_{\text{spin}} / (1 - D(\epsilon_F) U_{\text{eff}})$

χ^0_{spin} : Pauli Paramagnetism

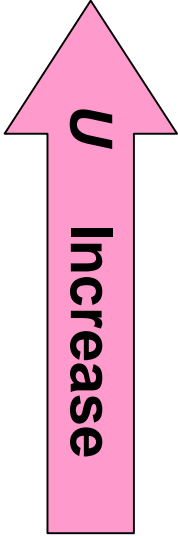
$D(\epsilon_F)$: Density of States at Fermi level

U_{eff} : effective U

Insulator: (4)

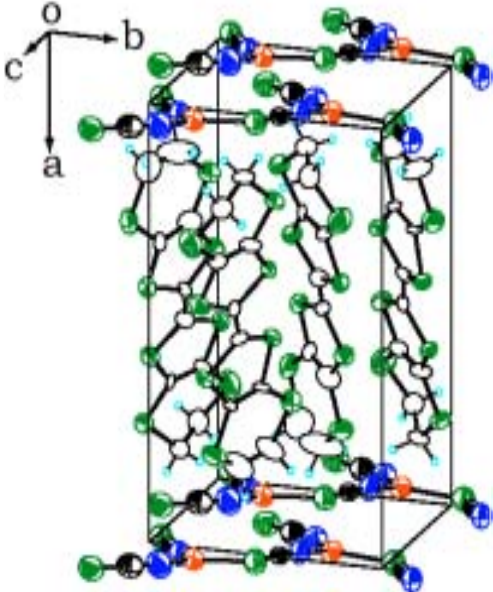
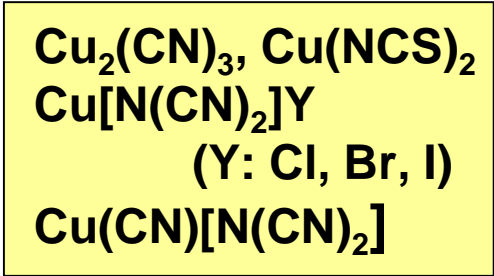
10K Super (Poor Metal)
(1), (2), (3) & (6)?

Good Metal: (5) $\beta\text{-(ET)}_2\text{AuI}_2$



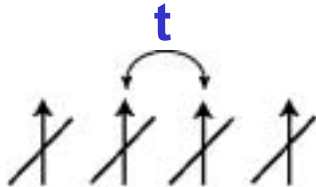
κ-Type 10 K Superconductor κ-(ET)₂X

X: polymerized anion

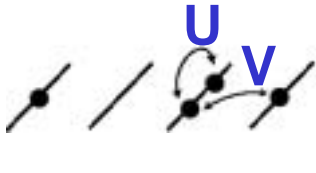
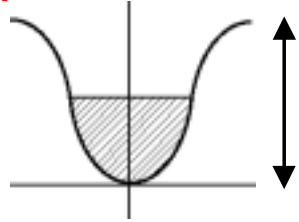


1) delocalization vs. localization (electron correlation)

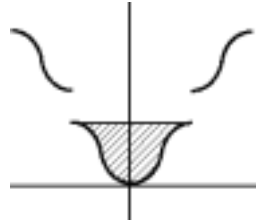
U/W



$U < W$

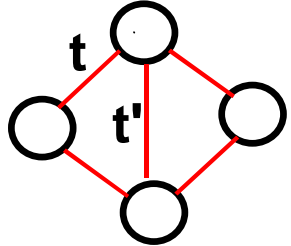
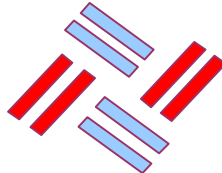
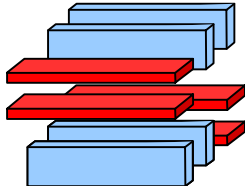


$U > W$



2) anisotropy

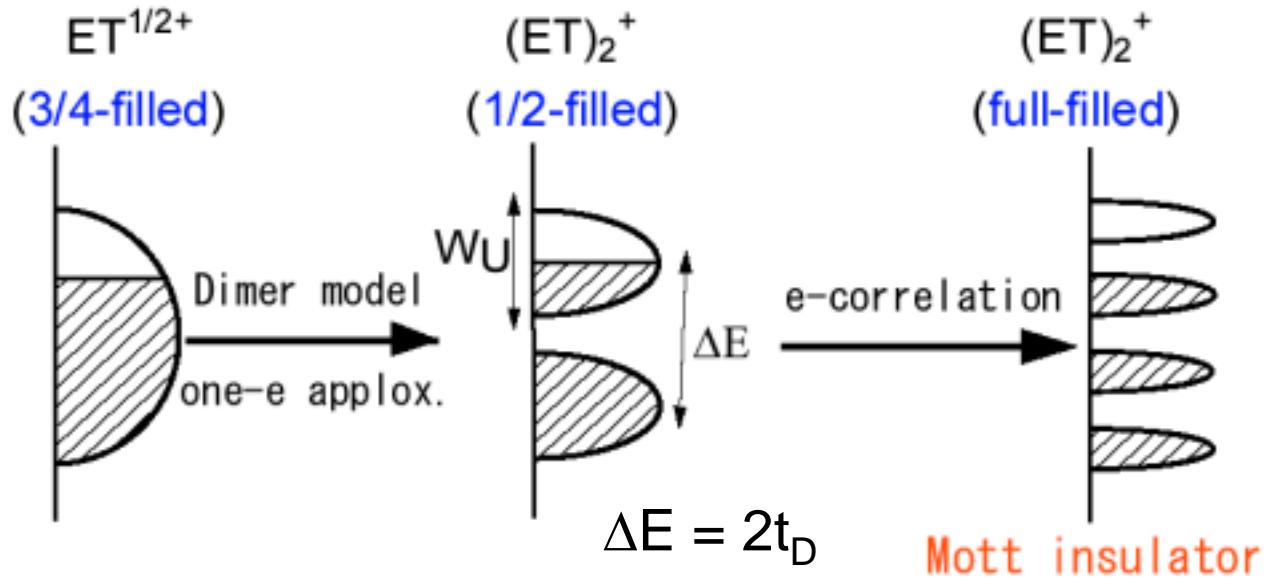
t'/t



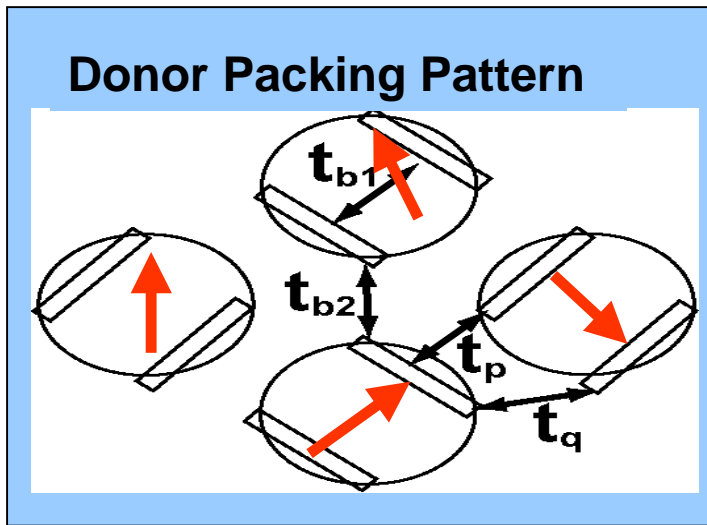
Electron correlation

Mott criterion for dimerized system: $W_u/\Delta E$ vs W_u

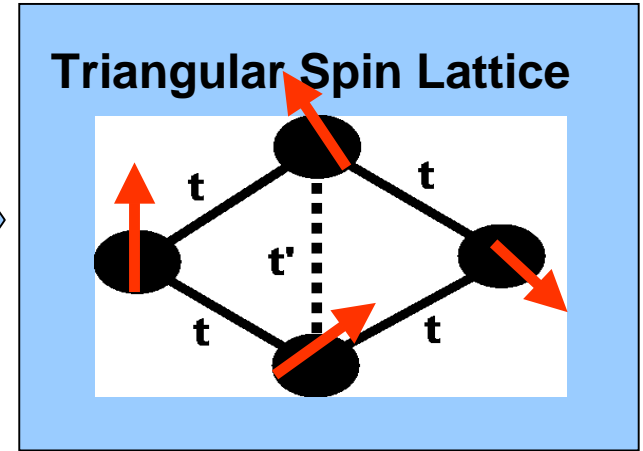
W_u : upper Hubbard band width, ΔE : dimerization energy



Anisotropy κ -(ET)₂X = *anisotropic triangular lattice*
 ET molecule = +0.5 \longrightarrow ET dimer has 1 spin



dimer model \longrightarrow

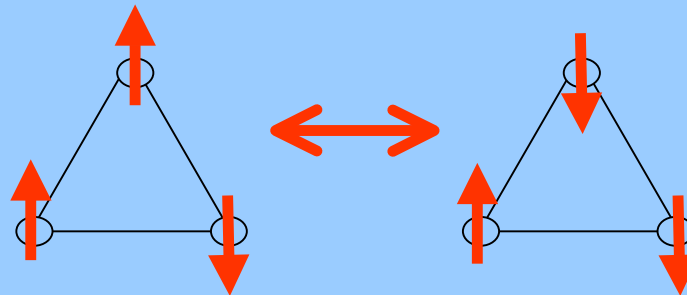


Large geometrical frustration between local spins when $t'/t \sim 1$

Ground state?

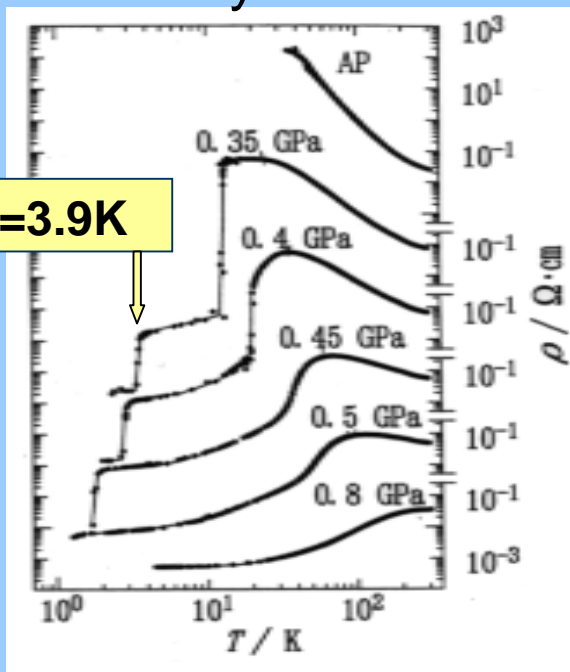
• **Antiferromagnet**

• **Spin liquid insulator (RVB)**



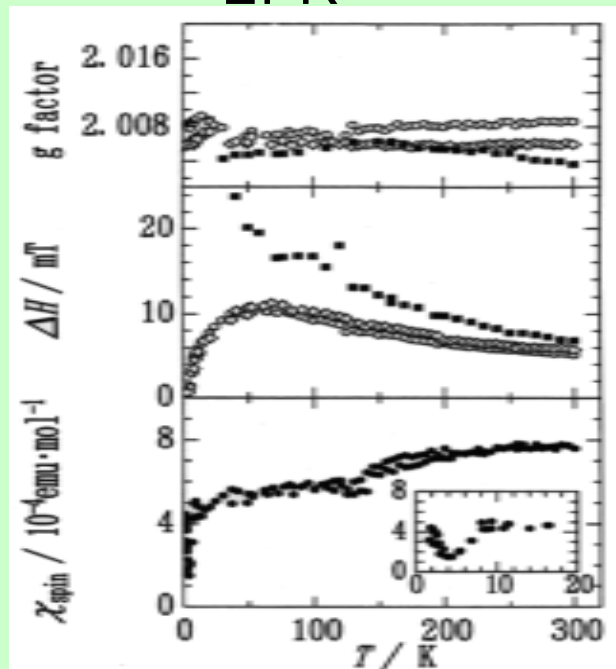
κ -(ET)₂Cu₂(CN)₃ **Uniform triangular lattice** → **Ground state ?**

Resistivity



$T_c = 3.9\text{K}$

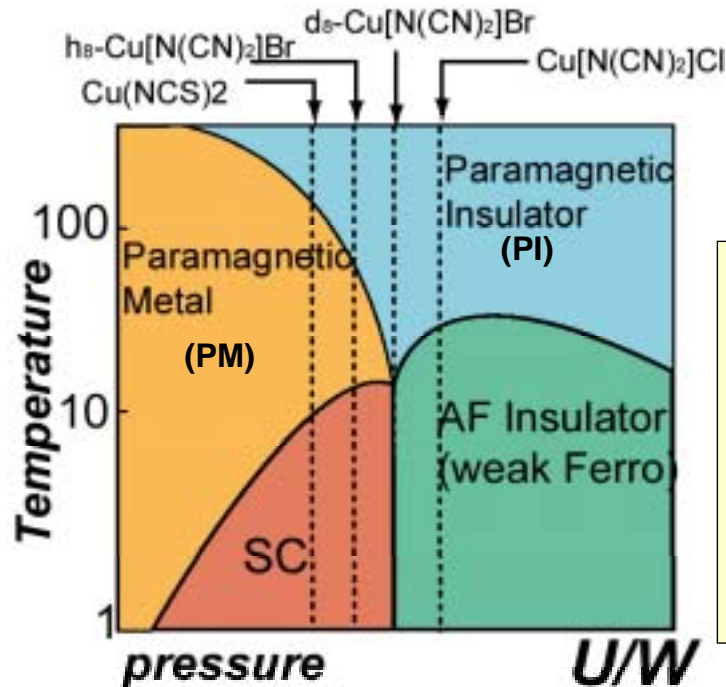
EPR



X	t'/t	ground state	T _c (K)	P _c (kbar)
Cu ₂ (CN) ₃	1.06	???	3.9	0.4
Cu[N(CN) ₂]Cl	0.75	Antiferro	12.8	0.3
d8-Cu[N(CN) ₂]Br	0.68	Antiferro		Rapid cool

T. Komatsu et al. JPSJ (1996), McKenzie, Comm. Cond. Mat. Phys. (1998)

κ -(ET)₂X *T - P* phase diagram



Spin-canting
Antiferromagnet (AF)
T=27 K

Only includes **U/W**

This phase diagram is not applicable to

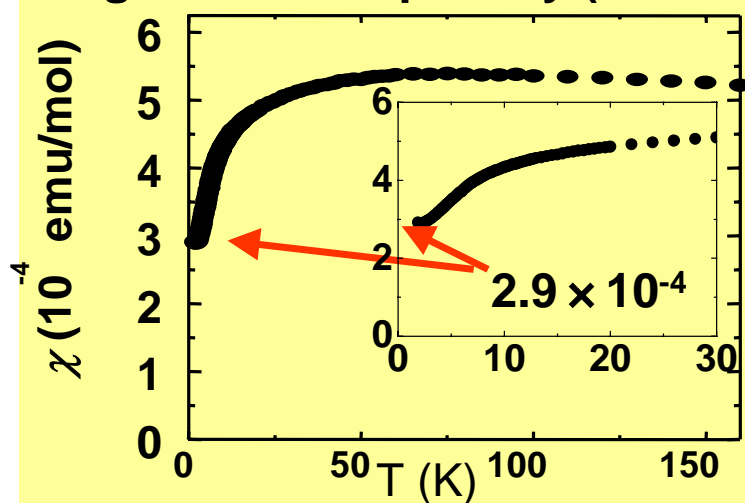
X=Cu(CN)[N(CN)]₂ (only PM and T_c=11.2 K)

X=Cu₂(CN)₃ (no AF but shows SC under pressure)

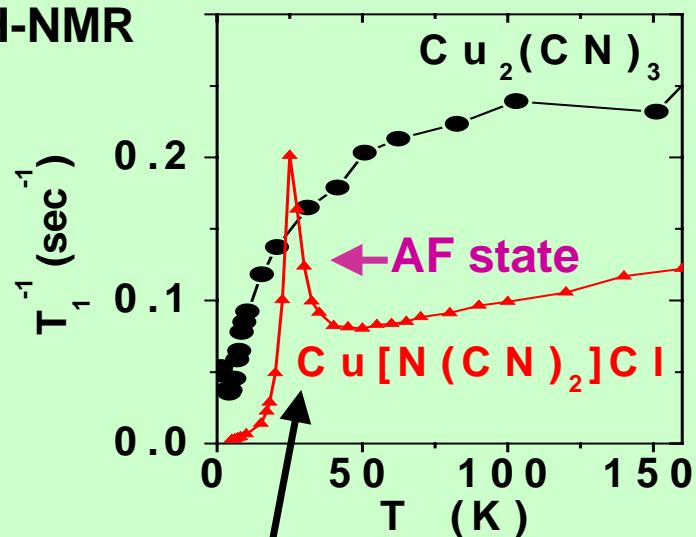
K.Kanoda 1997

Ground State of a Mott Insulator κ -(ET)₂Cu₂(CN)₃

Magnetic Susceptibility (SQUID)



¹H-NMR



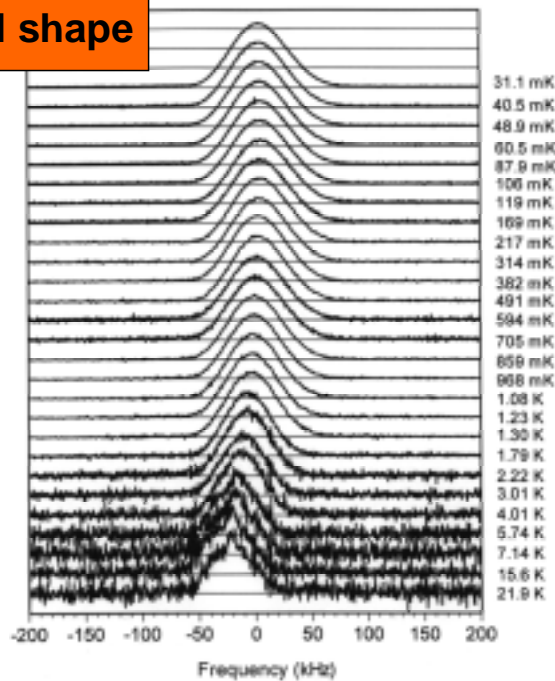
- ¹H-NMR ~ 31 mK
- SQUID ~ 1.9 K, 0.32 T
- EPR ~ 1.4 K
- μ SR 1.5 K - 20 mK

	t'/t	G state
Cu[N(CN) ₂]Cl	0.75	AF
(AF neighbors to SC state)		
Cu ₂ (CN) ₃	1.06	

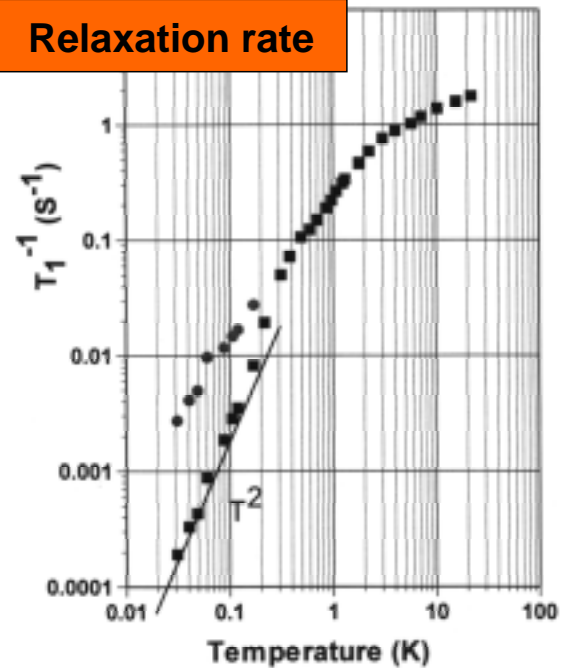
No Magnetic Order → **Spin-Liquid State**

**Very recent results $^1\text{H-NMR}$
(single crystal, $f_0=76.700\text{ MHz}$, $H_0=1.7967\text{T}$ 2D layer)**

Signal shape



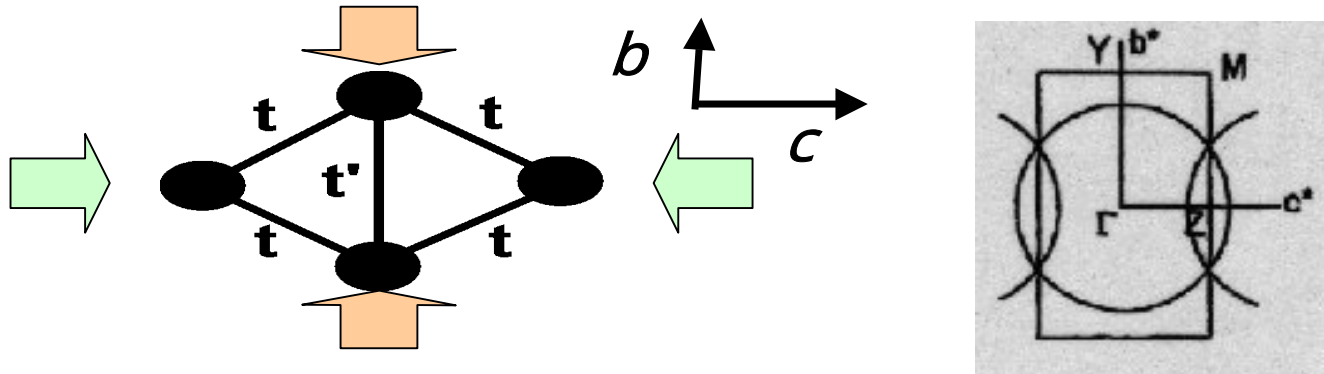
Relaxation rate



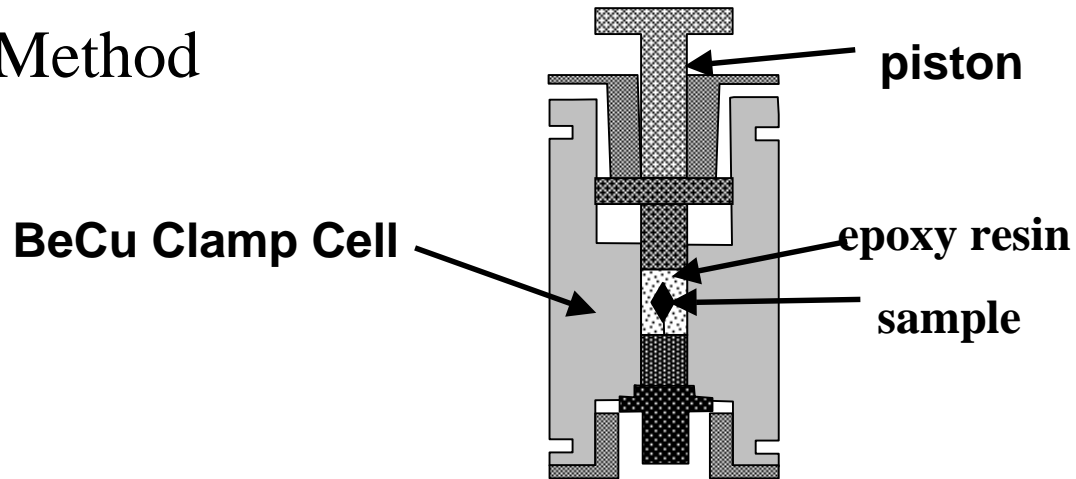
No Magnetic Order down to 30mK \longrightarrow **spin-liquid state**

Main signal () $T_1^{-1} \sim T^2$ \longrightarrow **Gapless**

Control of Triangular Anisotropy t'/t by Uniaxial Strain

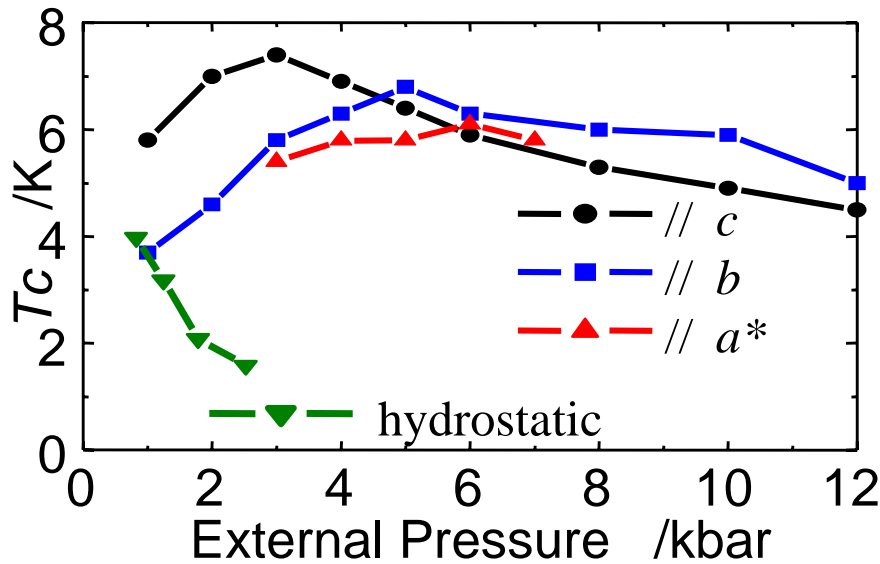
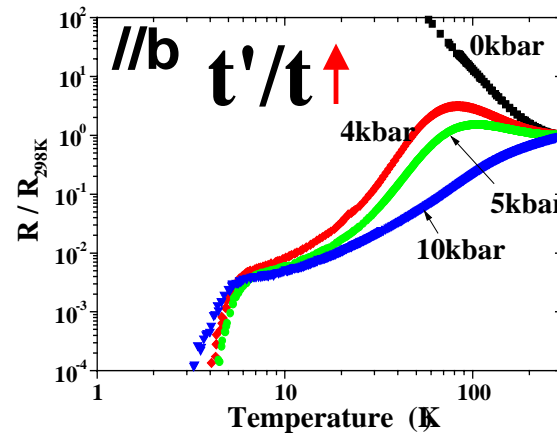
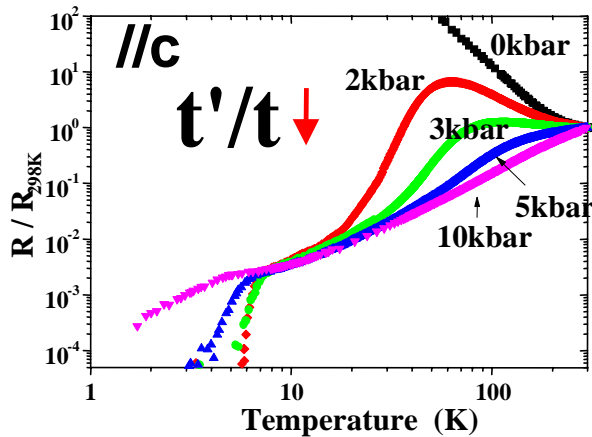


Maesato Method



Apply Stress Uniaxially without Poisson Effect

κ -(ET)₂Cu₂(CN)₃ Uniaxial Strain vs Hydrostatic Pressure



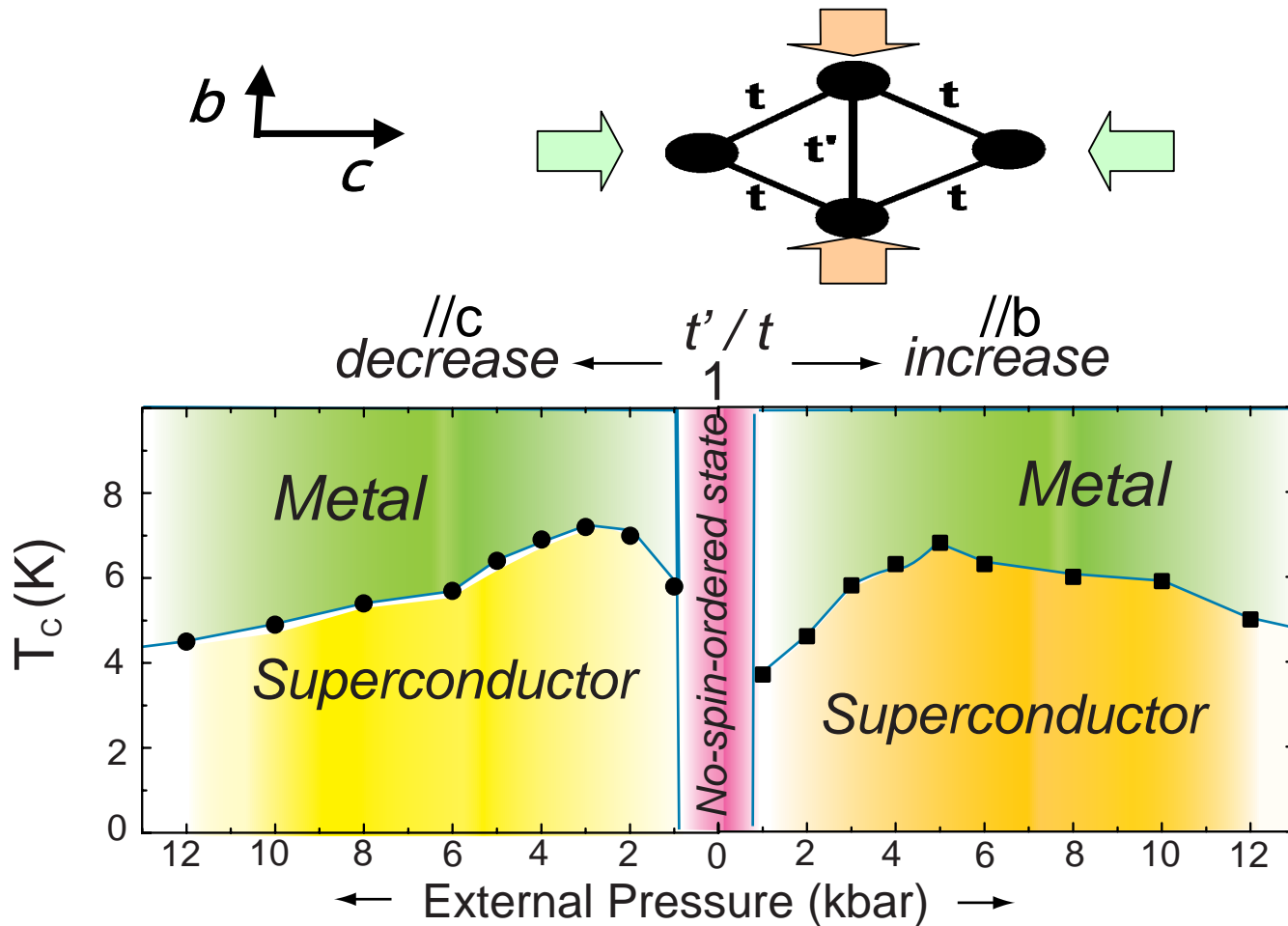
T_c under Uniaxial Strain

Increase in weak pressure
 in every direction

Anisotropic ($//c > //b > //a^*$)

Higher than under
 hydrostatic pressure

Uniaxial Strain on κ -(ET) $_2$ Cu $_2$ (CN) $_3$



Summary(2)

1. Ground state of a Mott insulator κ -(ET)₂Cu₂(CN)₃ is **Spin-Liquid State**

2. **Anisotropy t'/t** is critical for ground state of κ -(ET)₂X: spin-ordered AF vs. spin-disordered (spin-liquid) states

3. **Uniaxial Strain** vs ~~Hydrostatic~~
for Anisotropic Electronic State

A release of spin frustration in a spin-liquid state induces a superconducting state



Magnetic mediation

Molecular Design of Single Component Conductors

NATO

1. Introduction

Examples of Single Component Conductors

- a. Super under Pressure**
- b. Organometallic complexes**
- c. Neutral Closed Shell Compounds**
- d. Neutral Open Shell Compounds**
- e. Zwitter ionic (Betainic) Radicals**

2. On-Site Coulomb Repulsion

vs Mean-Free Path of Molecular Wire

3. Fused Mesomeric Betainic Radicals

4. Hydrogen Bond & Self-Complementarity

Many electrons in **nano-scale stage**
made of **soft & anisotropic media**

*molecular engineering,
pressure, doping*

Superconductivity
(non-BCS, anisotropic d_{xy})

Metal
low-dimensional
Fermi liquid

Molecular
deformation,
design, melting

Insulator

exotic magnetism

- AF order
- spin liquid
- spin ladder